

Jerzy Kanicki

1980 – 2015: Presentations at Professional Meetings, University and Industry

- *1980 – 1982: Universite Libre de Bruxelles, Bruxelles, Belgium*
- *1983 – 1994: IBM Thomas J Watson Research Center, Yorktown Heights, NY*
- *1994 – present: College of Engineering (EECS Department), University of Michigan, Ann Arbor, MI*

Contents:

- ✓ Invited Short Courses, Tutorials and Lectures
- ✓ Invited Conference Presentations
- ✓ Invited University and Industrial Seminars
- ✓ Invited Panelist
- ✓ Contributed Conference Presentations

INVITED SHORT COURSES, TUTORIALS AND LECTURES

1. **Int. Conf. on “Science and Technology of Display Phosphors,”** “*Organic Polymer Light-Emitting Devices and Displays on Plastic Flexible Substrates,*” J. Kanicki, Y. He, Y. Hong, Z. He, Z. Hong and A. Badano, November, 6-8, 2000, San Diego, CA.
2. **Society for Information Display, 2005 Int. Symposium One Day Seminar Lectures,** “*Organic Field-Effect Transistors for Flat Panel Displays,*” J. Kanicki, E. Cagin, M. Hamilton, H. Lee and P. Shea, May 23, 2005, Boston, MA.
3. **Society for Information Display, 26th International Display Research Conference,** “*Organic Field-Effect Transistors and Electronics,*” J. Kanicki, P.B. Shea and H. Lee, September 18, 2006, Kent, OH.
4. **Corning Display Workshop,** “*Organic and Oxide Semiconductor Thin-Film Transistors for Flat Panel Displays,*” J. Kanicki and P. Shea, October 26, 2006, Corning, NY.
5. **SID (Society for Information Display), 2008 Vehicles and Photons Symposium,** “*Amorphous Metal Oxide Thin-Film Transistors for Flexible Displays,*” J. Kanicki October 16-17, 2008, Dearborn, MI.
6. **SID (Society for Information Display), 2010 Vehicles and Photons Symposium,** “*Flexible Displays,*” J. Kanicki, October 21 – 22, 2010, Dearborn, MI.
7. **Ministry of International Trade and Industry (MITI),** Presentation to MITI Committee on “Flexible Displays” sponsored by “*Flexible Displays – US Status & Trend,*” J. Kanicki, January 20, 2010, Fukuoka, Japan.
8. **SID (Society for Information Display), 2011 Vehicles and Photons Symposium,** “*a-InGaZnO TFT for Future Active-Matrix Displays,*” J. Kanicki, October 20 – 21, 2011, Dearborn, MI.
9. **2012 China FPD Conference,** “*Amorphous InGaZnO Thin Film Transistors for Flat Panel Displays,*” J. Kanicki, March 21-22, 2012, Shanghai New International EXPO Center, Shanghai, China.
10. **Active-Matrix Flat Panel Displays and Devices – TFT Technologies and FPD Materials,** “*Electrical Stability of a-Si:H and a-InGaZnO Thin Film Transistors,*” J. Kanicki, The 19th International Workshop on July 4-6, 2012, Kyoto, Japan.
11. **SID (Society for Information Display) 2012 Vehicles and Photons Symposium,** “*Touchscreen Technology,*” J. Kanicki, October 18-19, 2012, Dearborn, MI.

INVITED CONFERENCE PRESENTATIONS

1. **International Conference on Conducting Polymers and the International CNRS Colloquium on the Physics and Chemistry of Synthetic and Organic Metals,** “*Review of Conductor – Polymeric Semiconductor Solar Cells,*” J. Kanicki, December 14-18, 1982, Les Arcs, France.
2. **1987 Materials Research Society Spring Meeting,** “*Metal/Hydrogenated Amorphous Silicon Interfaces,*” J. Kanicki, April 21-25, 1987, Palo Alto, CA.
3. **1988 American Physical Society March Meeting,** “*Material and Interface Issues in Hydrogenated Amorphous Silicon Thin-Film Transistor for Microelectronics,*” J. Kanicki, March 21-25, 1988, New Orleans, LA.

4. **International Topical Conference on Hydrogenated Amorphous Silicon Devices and Technology**, “*Metal/Hydrogenated Amorphous Silicon Interfaces*,” J. Kanicki, November 21-23, 1988, Yorktown Heights, NY.
5. **1989 Japan Society of Applied Physics Spring Meeting**, “*Properties of Device Quality Nitrogen-Rich Silicon Nitride Thin Films*,” J. Kanicki, April 1-4, 1989, Chiba, Japan.
6. **179th Electrochemical Society Meeting**, “*A Magnetic Resonance Investigation of Silicon Dangling Bonds in Silicon Nitride*,” W.L. Warren, P.M. Lenahan, F.C. Rong, E.H. Poindexter and J. Kanicki, May 5-10, 1991, Washington, D.C.
7. **15th Int. Conf. on Amorphous Semiconductors: Science and Technology**, “*Defects in Amorphous Hydrogenated Silicon Nitride Films*,” J. Kanicki and W.L. Warren, September 12-14, 1993, Cambridge, U.K.
8. **Active-Matrix Liquid Crystal Displays Symposium**, “*Amorphous Hydrogenated Silicon Thin Film Transistors: Physics and Technology*,” J. Kanicki, October 21-22, 1993, Bethlehem, PA.
9. **1993 Int. Semiconductor Device Research Symposium**, “*Bias Stress-Induced Instabilities in Amorphous Silicon Thin Film Transistors: Charge Trapping or Carrier-Induced Defect Creation*,” J. Kanicki and F.R. Libsch, December 1-3, 1993, Charlottesville, VA.
10. **1994 European Materials Society Spring Meeting**, “*a-Si:H TFT's Instability and Lifetime Requirements for AMLCD's*,” F.R. Libsch and J. Kanicki, May 24-27, 1994, Strasbourg, France.
11. **1995 American Vacuum Society Meeting**, “*Thin Film Transistor-Liquid Crystal Displays in the Year 2000*,” J. Kanicki, March 2, 1995.
12. **1995 American Chemical Society Fall Scientific Meeting on Materials for Emerging Technologies**, “*Thin-Film Transistor Liquid-Crystal Displays for the Year 2000*,” J. Kanicki, November 4, 1995, Midland, MI.
13. **1996 Materials Research Society Spring Meeting**, “*Flat Panel Display Materials*,” J. Kanicki, April 8-12, 1996, San Francisco, CA.
14. **26th European Solid-State Device Research Conf.**, “*High-Performance a-Si:H TFT for Large Area AMLCDs*,” C.-Y. Chen and J. Kanicki, September 9-11, 1996, Bologna, Italy.
15. **1996 Int. Active-Matrix Workshop**, “*Electrical Performance and Instability of High Field Effect Mobility a-Si:H TFTs Fabricated from High Deposition Rate PECVD Materials*,” C.-Y. Chen and J. Kanicki, September 30, 1996, Birmingham, U.K.
16. **Mardi Gras Conf. '97 on Multiscale Phenomena in Science and Engineering**, “*Materials for Flat Panel Displays*,” J. Kanicki, February 7-9, 1997, Baton Rouge, LA.
17. **Electronic Display Forum '97**, “*The Challenges of Research and Development in Universities on Flat Panel Displays and the Active Relationship Between Academia and Industry*,” J. Kanicki, April 16-18, 1997, Pacifico Yokohama, Japan.
18. **1997 Int. Workshop on Active-Matrix Liquid-Crystal Displays**, “*Gated-Four-Probe a-Si:H TFT Structure: a New Technique to Measure the Intrinsic Performance of a-Si:H TFT*,” C.-S. Chiang, C.-Y. Chen and J. Kanicki, September 11-12, 1997, Tokyo, Japan.

19. **1998 SPIE (The International Society for Optical Engineering) Conf. on Display Technologies II**, “*Planarization Technology of a-Si:H TFTs for AM-LCDs*,” J.-H. Lan and J. Kanicki, July 9-11, 1998, Taipei, Taiwan.
20. **Photonics China '98**, “*Viewing-Angle Improvement with Compensation Films for LCDs*,” G. Xu, A. Abileah, M. Jones, R. Brinkley, S.V. Thomsen, S. Gong and J. Kanicki, September 16-17, 1998, China.
21. **18th Int. Display Res. Conf. (Asia Display '98)**, “*Top-Gate a-Si:H TFT-LCD Technology: Past, Present and Future*,” J. Kanicki, S. Martin and Y. Ugai, September 28 – October 1, 1998, Seoul, Korea.
22. **The 6th International Conf. on the Science and Technology of Display Phosphors, Society for Information Display**, “*Organic Polymer Light-Emitting Devices and Displays on Plastic Flexible Substrate*,” J. Kanicki, Y. He, Y. Hong, Z. He, Z. Hong and A. Badano, November 6-8, 2000, San Diego, CA.
23. **2001 IS&T/SPIE 13th Int. Symposium on Electronic Imaging – Science and Technology**, “*a-Si:H Pixel Electrode Circuits for Active-Matrix Organic Light-Emitting Displays*,” J. Kanicki, Y. He and R. Hatori, January 21-26, 2001, San Jose, CA.
24. **2001 Materials Research Society Spring Meeting**, “*Amorphous Silicon Thin Film Transistor Pixel Electrode Circuits for Active-Matrix Organic Light-Emitting Displays*,” J. Kanicki and J. Kim, April 16-20, 2001, San Francisco, CA.
25. **Asia Display/International Display Workshops'01**, “*Amorphous Silicon Thin-Film Transistors Based Active-Matrix Organic Light-Emitting Displays*,” J. Kanicki, J.-H. Kim, J.Y. Nahm, Y. He and R. Hatori, October 10-19, 2001, Nagoya, Japan.
26. **2001 Int. Conf. on the Science and Technology of Emissive Displays and Lighting**, “*Organic Polymer Light Emitting Devices on Plastic Substrates*,” J. Kanicki, Y. Hong, Z. He, S. Lee, and A. Badano, November 12-14, 2001, San Diego, CA.
27. **American Chemical Society – 2002 Great Lakes Regional Meeting**, “*Organic Polymer Light-Emitting Devices on Plastic Substrates for Active-Matrix Organic Polymer Light-Emitting Displays*,” J. Kanicki, Y. Hong, and S. Lee, June 2-4, 2002, Minneapolis, MN.
28. **2002 International Workshop on Active-Matrix Liquid-Crystal Displays**, “*Three a-Si:H TFT Pixel Electrode Circuit for AM-OLEDs*,” J. Kanicki and J.-H. Kim, July 10-12, 2002, Tokyo, Japan.
29. **2003 Materials Research Society Spring Meeting**, “*200 dpi a-Si:H TFT Active Matrix Organic Polymer Light-Emitting Displays*,” J. Kanicki and Y. Hong, April 21-25, 2003, San Francisco, CA.
30. **2003 Flat Panel Display International**, “*a-Si:H TFTs Active-Matrix Organic Polymer Light-Emitting Displays*,” J. Kanicki, October 29-31, 2003, Pacifico Yokohama, Japan.
31. **24th Int. Display Research Conference and 4th Int. Meeting on Inf. Display**, “*Organic Polymer Light-Emitting Devices on a Flexible Plastic Substrate*,” J. Kanicki, S.J. Lee, Y. Hong and C.C. Su, August 23-27, 2004, Daegu, Korea.
32. **2005 Int. Conf. on Solid-State Devices and Materials**, “*Tetrabenzoporphyrin Organic Semiconductors for Flexible Organic Thin Film Transistors and Circuits*,” P. Shea, J. Kanicki and N. Ono, September 13-15, 2005, Kobe, Japan.

33. **Society of Information Display, 2005 Vehicle Display Symposium**, “*Opto-electric Properties of a-Si:H TFTs 100 dpi Active-Matrix Polymer Light-Emitting Display*,” J. Kanicki, October 6-7, 2005, Dearborn, MI.
34. **2006 Materials Research Society Spring Meeting, Symposium on “Materials for Next Generation Display Systems,”** “*Inorganic Semiconductor Thin-Film Transistors for Flat Panel Displays*,” J. Kanicki, H. Lee, A. Kuo, J. Siddiqui, C. Chen and J. Phillips, April 18-20, 2006, San Francisco, CA.
35. **13th Int. Workshop on Active-Matrix Flat Panel Displays and Devices – TFT Technologies and Related Materials**, “*Thermal and Electrical Instability of Amorphous Silicon Thin-Film Transistors for AM-FPDs*,” A. Kuo and J. Kanicki, July 5-7, 2006, Tokyo, Japan.
36. **IDMC’07 (International Display Manufacturing Conference & FPD Expo)**, “*Novel Pixel Electrode Circuits and a-Si:H TFT Structures for AM-OLEDs*,” H. Lee, J.S. Yoo, C.-D. Kim, I. Kang and J. Kanicki, July 3-6, 2007, Taipei International Convention Center, Taiwan.
37. **International Workshop on Transparent Amorphous Oxide Semiconductors TACOS 2010**, “*A-IGZO Density of States: Photo-Field Effect and Temperature Dependence Studies*,” T.C. Fung, C. Chen and J. Kanicki, January 25-26, 2010, Tokyo Institute of Technology, Yokohama, Japan.
38. **6th International Thin – Film Transistor Conference**, “*Electrical Stability of Advanced a-Si:H TFT Structures*,” G. Yoo, H. Lee and J. Kanicki, January 28 – 29, 2010, Egret, Himeji, Japan.

INVITED UNIVERSITY AND INDUSTRIAL SEMINARS

1. **Journees d'Etudes d'Electrochimie**, “*Photovoltaisme des Jonctions Metal-Semiconducteur Organique*,” J. Kanicki and J. M. Dohan, 27-29 April 1981, Macon, France.
2. **N.F.W.O.-F.N.R.S. Contact Group Molecular Photochemistry**, “*Optical, Electrical and Photovoltaic Properties of trans-Polyacetylene*,” Boue, J.M. Dohan, P. Fedorko, J. Kanicki and E. Vander Donckt, March 1982, Brussels, Belgium.
3. **Chronar Corp.**, “*Schottky Barrier Polyacetylene Solar Cells*,” J. Kanicki, Princeton, September 23, 1983, NJ.
4. **Xerox Webster Research Center**, “*Homogeneous Chemical Vapor and Plasma Deposition in Amorphous Silicon Technology*,” J. Kanicki and B.A. Scott, November 9, 1983, Rochester, NY.
5. **Exxon Corp.**, “*HOMOCVD Deposited Films and Their Application in Photovoltaic Devices*,” J. Kanicki and B.A. Scott, Linden, November 15, 1983, NJ.
6. **IBM Thomas J. Watson Research Center**, “*Metal/a-Si:H Contacts*,” J. Kanicki, Yorktown Heights, February 17, 1984, NY.
7. **1984 New York State University Spring Seminar Series**, “*Metal-Polyacetylene Schottky Barrier Diodes*,” J. Kanicki, April 13, 1984, Buffalo, NY.
8. **TFT-LCD's IBM Program Planning Meeting**, “*Review on TFT Processing and Current Status*,” J. Kanicki, August 28-29, 1984, Kingston, NY.
9. **IBM Eastview Research Laboratory**, “*Metal/Amorphous Silicon Contacts*,” J. Kanicki and D.B. Bullock, October 1985, Eastview, NY.

10. **IBM Eastview Research Laboratory**, "*Materials and Metallization Requirements for Active-Matrix Devices*," J. Kanicki, July 7, 1986, Eastview, NY.
11. **IBM Almaden Research Center**, "*Comparative Study of PECVD Nitride Films*," J. Kanicki, October 27, 1986, Almaden, CA.
12. **United Technologies Research Center**, "*Material Analysis of Silicon Nitride Films Deposited in Various PECVD Systems*," J. Kanicki, November 12, 1986, East Hartford, CT.
13. **Pennsylvania State University**, "*Metal/Hydrogenated a-Si:H Contacts*," J. Kanicki, November 19, 1986, University Park, PA.
14. **1987 Amorphous Silicon Subcontractors' Review Meeting**, "*The Contact Issue in the Hydrogenated Amorphous Silicon Technology*," J. Kanicki, January 26-27, 1987, Palo Alto, CA.
15. **Xerox Palo Alto Research Center**, "*Properties of Hydrogenated Amorphous Silicon Nitride Films Deposited in Various PECVD Systems*," J. Kanicki, November 2, 1987, Palo Alto, CA.
16. **University of North Carolina**, "*Metal/Hydrogenated Amorphous Silicon Interfaces*," J. Kanicki, November 17, 1987, Chapel Hill, NC.
17. **North American Philips Corporation**, "*The Contacts Issues in the Hydrogenated Amorphous Silicon Thin-Film Transistor Technology*," J. Kanicki, November 24, 1987, Briarcliff Manor, NY.
18. **T. J. Watson Research Laboratory**, "*Comparative Study of PECVD Nitride Films*," J. Kanicki, December 4, 1987, Yorktown Heights, NY.
19. **IBM East Fishkill Seminar Series**, "*Microcrystalline Silicon: Material Properties and Applications*," J. Kanicki, April 28, 1988, East Fishkill, NY.
20. **Seminar Series of Institute of Energy Conversion, University of Delaware**, "*Material and Interface Issues in Hydrogenated Amorphous Silicon Thin Film Transistors*," J. Kanicki, May 19, 1988, Newark, DE.
21. **Trench Workshop III - Trench Fill**, "*Hydrogenated Amorphous Silicon: Preparation, Properties and Applications*," J. Kanicki, IBM East Fishkill, June 1-3, 1988, NY.
22. **Seminar Series of Sherman Fairchild Center**, "*Lehigh University Material and Interface Issues in Hydrogenated Amorphous Silicon Thin Film Transistors*," J. Kanicki, June 22, 1988, Bethlehem, PA.
23. **IBM Yamato Development Laboratory**, "*Highly Conductive P-doped Microcrystalline Silicon*," J. Kanicki, July 1988, Japan.
24. **TFT/LCD IBM Review Meeting**, "*Microcrystalline TFT's Contacts*," J. Kanicki, March 16-17, 1989, Eastview, NY.
25. **IBM Yamato Laboratory**, "*Properties of Undoped and Phosphorous Doped Microcrystalline Silicon Thin Films*," J. Kanicki, April 4, 1989, Yamato, Japan.
26. **IBM Yamato Laboratory**, "*Properties of N-rich Amorphous Silicon Nitride Thin Films*," J. Kanicki, April 5, 1989, Yamato, Japan.
27. **Toshiba Research and Development Center**, "*Properties of Device Quality Nitrogen-Rich Silicon Nitride Thin Films*," J. Kanicki, April 6, 1989, Kawasaki, Japan.

28. **Matsushita Electric Central Center Research Laboratory**, “*Properties of Device Quality Nitrogen-Rich Silicon Nitride Thin Films*,” J. Kanicki, April 7, 1989, Osaka, Japan.
29. **Tokyo Institute of Technology**, “*Properties of Undoped and Phosphorous Doped Microcrystalline Silicon Thin Films*,” J. Kanicki, April 10, 1989, Tokyo, Japan.
30. **Electrotechnical Laboratory Center**, “*Properties of Device Quality Nitrogen-Rich Silicon Nitride Thin Films*,” J. Kanicki, April 11, 1989, Tsukuba, Japan.
31. **IBM Research Seminar Series**, “*Amorphous Silicon Thin Film Transistor Technology*,” J. Kanicki, May 19, 1989, Yorktown Heights, NY.
32. **University "La Sapienza" of Rome**, “*Properties of Dielectric Films Deposited by Plasma-Enhanced Chemical Vapor Deposition*,” J. Kanicki, September 22, 1989, Rome, Italy.
33. **Institute of Electronic of the Solid State**, “*Materials and Interface Issues in Hydrogenated Amorphous Silicon Thin Film Transistor*,” J. Kanicki, September 25, 1989, Rome, Italy.
34. **Interuniversities Micro-Electronic Center**, “*Observation of the Silicon Nitride Interface Properties on Crystalline and Amorphous Silicon Interface*,” J. Kanicki, October 3, 1989, Leuven, Belgium.
35. **Institute of Thin Film and Ion Technology**, “*Interface States at the Silicon Nitride/Amorphous and Crystalline Silicon Interfaces*,” J. Kanicki, October 9, 1989, Julich, Germany.
36. **1989 IBM ASTL Symposium**, “*How to Control and Improve Polysilicon Emitter*,” J. Tien, P. Ronsheim, T. Walker, T. Smutek, D. E. Kotecki, S.J. Jeng, J. Kanicki, C.C. Parks, W. Rausch, E. Grabbe, K. Seshan, L. Prabhu, and B.W. Hicks, November 7-9, 1989, East Fishkill, NY.
37. **1989 IBM ASTL Symposium**, “*Properties of in-Situ Phosphorous-doped Hydrogenated Microcrystalline Silicon and its Application as a Wide-Grain Emitter Material*,” D. E. Kotecki, S.J. Jeng, J. Kanicki, C.C. Parks, W. Rausch, K. Seshan and J. Tien, November 7-9, 1989, East Fishkill, NY.
38. **IBM Eastview Laboratory**, “*Light-Induced ESR in Nitrogen-Rich Gate-Quality Amorphous Silicon Nitride Films*,” M.S. Crowder, E.D. Tober, J. Kanicki and D. Jousse, December 1989, Eastview, NY.
39. **IBM Eastview Laboratory**, “*Stretched-Exponential Illumination Time Dependence of Positive Charge and Spin Generation by Subbandgap UV-light in Amorphous Silicon Nitride Films*,” J. Kanicki, M. Sankaran, A. Gelatos, M.S. Crowder, E.T. Tober, March 5, 1990, Eastview, NY.
40. **IBM Eastview Laboratory**, “*Performance of the 55 nm Amorphous Silicon TFT*,” J. Kanicki, J. Griffith, and R. Polastre, March 12, 1990, Eastview, NY.
41. **IBM Research Division Seminar Series**, “*Structure of Trapping Centers in Silicon Nitride*,” P.M. Lenahan, D.T. Krick, W.L. Warren, S. Curry and J. Kanicki, April 6, 1990, Eastview, NY.
42. **1990 Spring Masterslice Seminar Series**, “*Hydrogenated Amorphous Silicon Thin Film Transistors: Physics, Properties and Applications*,” J. Kanicki, May 1, 1990, East Fishkill, NY.
43. **IBM Department 600 Accomplishment Review Meeting**, “*Nature of Defects and Kinetics of Trapping in N-rich Amorphous Silicon Nitride*,” J. Kanicki, November 26, 1990, Eastview, NY.
44. **1990 IBM ASTL Symposium**, “*Properties, Structure and Application of in-Situ Phosphorous Doped Hydrogenated Microcrystalline Silicon*,” S.T. Jeng, D.E. Kotecki, J. Kanicki, C.C. Parks, J. Tien and L. Prabhu, December 1990, East Fishkill, NY.

45. **The Pennsylvania Surface Science Workshop**, “*Polysilicon Film/Gate Oxide Interface of Polycrystalline Silicon Thin Film Transistors*,” J.H. Jung, S. Lin, M. Hatalis and J. Kanicki, May 15, 1991, Bethlehem, PA.
46. **Computer Science and Electrical Engineering Seminar Series, Lehigh University**, “*Hydrogenated Amorphous Silicon Thin Film Transistors for Flat Panel Displays*,” J. Kanicki, October 9, 1991, Bethlehem, PA.
47. **Princeton University, EMD Seminar Series**, “*Thin Film Transistors: Physics, Properties and Applications*,” J. Kanicki, April 5, 1993, Princeton, NJ.
48. **IBM Entry System Technologies Laboratory Accomplishments Meeting**, “*a-Si:H TFT Electrical Stability*,” F. Libsch and J. Kanicki, May 12, 1993, Eastview, NY.
49. **AT&T Laboratories, Flat Panel Display Seminar Series**, “*Low Temperature Materials for Thin Film Transistors*,” J. Kanicki, December 14, 1993, Murray Hill, NJ.
50. **Center for Display Technology & Manufacturing, University of Michigan**, “*Thin Film Transistors for Liquid Crystal Flat Panel Displays*,” J. Kanicki, December 17, 1993, Ann Arbor, MI.
51. **Toshiba Corp.**, “*UV-Light Induced Changes in Polyimide LC Alignment Films*,” J. Kanicki, August 31, 1995, Kawasaki, Japan.
52. **IBM Japan Ltd.**, “*Simulation of the High Performance a-Si:H TFT for High Definition LCDs*,” J. Kanicki, August 31, 1995, Yamamoto, Japan.
53. **Sharp Corp.**, “*a-Si:H TFTs*,” J. Kanicki, August 28, 1995, Osaka, Japan.
54. **NEC Corp.**, “*Simulation of the High Performance a-Si:H TFT for High Definition LCDs*,” J. Kanicki, August 30, 1995, Tokyo, Japan.
55. **Hosiden Corp.**, “*Simulation of the High Performance a-Si:H TFT for High Definition LCDs*,” J. Kanicki, August 29, 1995, Kobe, Japan.
56. **DTI Inc.** “*Simulation of the High Performance a-Si:H TFT for High Definition LCDs*,” J. Kanicki, August 29, 1995, Tokyo, Japan.
57. **Hitachi Ltd.**, “*a-Si:H TFTs*,” J. Kanicki, August 30, 1995, Tokyo, Japan.
58. **Annual Meeting of the Society of Motion Picture and Television Engineers**, “*Thin-Film Transistor Liquid-Crystal Displays for Year 2000*,” J. Kanicki, February 13, 1996, Southfield, MI.
59. **Dow Chemical Corp.**, “*Planarization of a-Si:H TFTs*,” J. Kanicki, November 18-19, 1997, Midland, MI.
60. **Physics Seminar at Ford Corp.**, “*Reflective and OLED Based Flat Panel Displays*,” J. Kanicki, November 5, 1998, Dearborn, MI.
61. **Dow Corning Corp.**, “*Spin-coated Flowable Oxide for AMLCD*,” J. Kim and J. Kanicki, January 29, 1999, Midland, MI.
62. **Kodak Research Laboratories**, “*Amorphous Silicon Based AM-OLEDs*,” J. Kanicki, October 16, 2000, Rochester, N.Y.
63. **Optical Society of America**, “*Organic Polymer Light-Emitting Devices and Displays*,” J. Kanicki, October 17, 2000, Ann Arbor, MI.

64. **Hope College**, “*Organic Polymer Light-Emitting Devices and Displays*,” J. Kanicki, January 12, 2001, Holland, MI.
65. **Dow Corning Corp.**, “*Organic Polymer Light-Emitting Devices on Plastic Substrates*,” J. Kanicki, S.J. Lee and Y. Hong, February 2004, Midland, MI.
66. **LG. Phillips LCD**, “*AM-PLEDs Based on a-Si:H TFTs*,” J. Kanicki, August 30, 2004, Anyang-Shi, Gyonggi-do, Korea.
67. **LG. Phillips LCD**, “*a-Si:H TFT AM-PLEDs*,” J. Kanicki, August 27, 2004, Kumi-city, Kyunbuk, Korea.
68. **Samsung Advanced Institute of Technology**, “*Organic Polymer Light-Emitting Devices on Flexible Plastic Substrate*,” J. Kanicki, Y. Hong, S.J. Lee and H. Lee, August 31, 2004, Yongin-si, Gyeonggi-do, Korea.
69. **Samsung SDI**, “*a-Si:H TFT Back Plane for AM-OLEDs*,” J. Kanicki, J. Kim and Y. Hong, August 31, 2004, Yongin-si, Gyeonggi-do, Korea.
70. **Samsung Electronics Co., LTD**, “*a-Si:H TFT AM-PLEDs*,” J. Kanicki, J. Kim and Y. Hong, September 1, 2004, Yongin-si, Gyeonggi-do, Korea.
71. **Air Force Research Laboratory**, “*Organic Polymer Devices on Flexible Plastic Substrates*,” J. Kanicki, Y. Hong, S.J. Lee and H. Lee, November 19, 2004, Wright-Paterson, AFB, OH.
72. **Matsushita Electric Industrial Co., Ltd**, “*Tetrabenzoporphyrin-Based Field-Effect Transistors*”; & “*White Light-Emitting Device on Flexible Plastic Substrates*,” P. Shea, J. Kanicki and H. Lee, September 13, 2005, Osaka, Japan.
73. **Sanyo Electric Co., Ltd**, “*Organic Polymer Thin-Film Transistors*,” J. Kanicki, P. Shea and M. Hamilton, September 16, 2005, Osaka, Japan.
74. **Ehime University**, “*Tetrabenzoporphyrin-Based Field-Effect Transistors*,” P.B. Shea and J. Kanicki, September 17, 2005, Matsuyama, Japan.
75. **Dow Corning Corp. Seminar Series**, “*Organic Polymer Light-Emitting Devices on Plastic Substrate*,” J. Kanicki, Y. Hong and H. Lee, February 2, 2006, Midland, MI.
76. **University of Tokyo**, “*Electronic Properties of Porphyrin-Based Organic Transistors*,” J. Kanicki and P. Shea, July 7, 2006, Tokyo, Japan.
77. **Ehime University**, “*Solution Processed Organic Semiconductors for Flexible Organic Thin Film Transistors and Circuits*,” J. Kanicki, July 10, 2006, Matsuyama, Japan.
78. **3M Corp. Seminar Series**, “*White-Light and Thin-Film Transistors for Future Flat Panel Displays*,” J. Kanicki, October 20, 2006, Minneapolis-St. Paul, MN.
79. **Toppan Printing Co.**, “*Organic Semiconductor Thin-Film Transistors for Flat Panel Displays*,” J. Kanicki and P.B. Shea, July 2, 2007, Saitama, Japan.
80. **Tokyo Institute of Technology**, “*a-Si:H TFTs versus a-IGZO TFTs*,” J. Kanicki, July 2, 2007, Tokyo, Japan.
81. **Fuji Electric Advanced Technology Co., Ltd.**, “*Organic Semiconductor Thin-Film Transistors for Flat Panel Displays*,” J. Kanicki and P.B. Shea, July 3, 2007, Tokyo, Japan.

82. **Canon Inc.**, Canon Research Center, “*Advanced a-Si:H TFTs for Flat Panel Displays*,” J. Kanicki, P. Ahn and A. Kuo, July 3, 2007, Tokyo, Japan.
83. **Ministry of International Trade and Industry (MITI)**, “*Flexible Displays- US Status & Trend*,” J. Kanicki, January 20, 2010, Fukuoka, Japan.
84. **Canon Inc.**, Canon Research Center, “*A-In-Ga-Zn-O for Future Flat Panel Displays*,” J. Kanicki, C. Chen and R. Fung, January 21, 2010, Tokyo, Japan.
85. **Sharp Corp.**, Advanced Technology Development Center, “*2D Numerical Simulation, BTS, and CTS of Amorphous In-Ga-Zn-O Thin Film Transistors*,” J. Kanicki, January 26, 2010, Tenri, Nara, Japan.
86. **Qualcomm Inc.**, Qualcomm Research Center, “*Amorphous In-Ga-Zn-O Thin Film Transistor for Future Optoelectronics*,” J. Kanicki and T.-C. Fung, July 28, 2010, San Diego, CA.
87. **Univ. of Michigan – Shanghai Jiao Tong Univ. Joint Institute**, “*Amorphous InGaZnO Thin-Film Transistors for Flat Panel Displays*,” J. Kanicki, March 23, 2012, Shanghai, China.
88. **Shanghai Tianma**, “*Amorphous InGaZnO Thin-Film Transistors for Flat Panel Displays*,” J. Kanicki, March 23, 2012, Shanghai, China.
89. **NHK Science and Technology Laboratories**, “*Electrical Stability of a-Si:H and a-InGaZnO Thin Film Transistors*,” J. Kanicki, June 29, 2012, Tokyo, Japan.
90. **Sony Corp.**, “*Amorphous InGaZnO Thin Film Transistors for Flat Panel Displays*,” J. Kanicki, July 3, 2012, Astugi, Japan.
91. **Siemens AG, Corporate Technology**, “*Amorphous In-Ga-Zn-O Thin-Film Transistor Active Pixel Sensor X-ray Imager for Digital Breast Tomosynthesis*,” Chumin Zhao and Jerzy Kanicki, July 15, 2013, Erlangen, Germany.
92. **FDA (U.S. Food and Drug Administration)**, “*Future Digital Tomosynthesis: Organic Photo-detector / a-InGaZnO Thin – Film Transistor Active Matrix Pixel Sensor Imager*,” Chumin Zhao and Jerzy Kanicki, July 18, 2014, Silver Spring, MD.
93. **STFC (Science and Technology Facilities Council)**, “*Organic Photodetector / a-InGaZnO TFT Active Pixel Sensor for X-ray Imaging*,” Jerzy Kanicki, Rutherford Appleton Laboratory, Harwell Campus, September 2, 2014, Didcot, UK.
94. **IMEC (Interuniversity MicroElectronics Center)**, “*a-IGZO TFT for High Resolution Flat Panel Displays*,” Jerzy Kanicki, August 29, 2014, Leuven, Belgium.

INVITED PANELIST

1. **2005 Int. Conf. on Solid-State Devices and Materials (SSDM 2005)**, “*Flexible Electronics – Is It Real?*” J. Kanicki, September 14, 2005, Kobe, Japan.

CONTRIBUTED CONFERENCE PRESENTATIONS

1. **VIII IUPAC Symposium on Photochemistry**, “*The poly-2-Vinylpyridine Iodine Complex-SnO₂ System Under Near U.V. and Visible Light Irradiation*,” B. Noirhomme, J. Kanicki and E. Vander Donckt, July 13-19, 1980, Seefeld, Austria.
2. **International Conference on Low Dimensional Synthetic Metals**, “*Relation Between Optical and Electrical Properties of the trans-CH_x-Iodine Complex: Variable Range Hopping*,” J. Kanicki, August 10-15, 1980, Helsingor, Denmark.
3. **Congres de la Societe Francaise de Physique**, “*Relation Entre les Proprietes Optique et Electriques du Polyacetylene Dope par les Halogenes*,” J. Kanicki, E. Vander Donckt et S. Boue, June 29-July 4, 1981, Clermont-Ferrand, France.
4. **International Conference on Low-Dimensional Conductors**, “*Photovoltaic and Rectification Properties of In / trans-CH_x Electrode +502 Schottky-Barrier Cells*,” J. Kanicki, S. Boue and E. Vander Donckt, August 10-14 1981, Boulder, CO.
5. **2nd General Conference of the Condensed Matter Division of the European Physical Society**, “*Contact Properties Between Undoped trans-Polyacetylene and Metals*,” J. Kanicki, P. Fedorko, S. Boue and E. Vander Donckt, March 22-25, 1982, Manchester, U. K.
6. **Symposium on Conducting Polymers at the American Chemical Society Meeting**, “*Organic Photovoltaic Materials*,” J. Kanicki, May 10-14, 1982, Stresa, Italy.
7. **Symposium on Order in Polymeric Materials: Implications for Electronic, Metals-Magnetic, and Optical Phenomena**, “*Metals Polyacetylene Schottky Barrier Diodes*,” J. Kanicki, August 25-26, 1983, GTE Laboratories, Waltham, MA.
8. **4th EC Photovoltaic Solar Energy Conference**, “*Organic Photovoltaic Materials*,” J. Kanicki, May 10-14, 1982, Stresa, Italy.
9. **64th Meeting of the Electrochemical Society**, “*Hydrogenated Amorphous Silicon Schottky Barrier Structures Prepared by Homogeneous Chemical Vapor Deposition*,” J. Kanicki, J.F. Nijs, B.A. Scott, R.M. Plecenick and B.S. Meyerson, October 9-14, 1983, Washington, D.C.
10. **Fifth EC Photovoltaic Solar Energy Conference**, “*Amorphous Hydrogenated Silicon Solar Cells with the Homogeneous CVD Technique*,” F. Nijs, J. Kanicki, B.A. Scott, R.M. Plecenick and B.S. Meyerson, October 17-21, 1983, Kavouri Bay, Athens, Greece.
11. **International Topical Conference on Transport and Defects in Amorphous Semiconductors**, “*Transport Properties and Defect States of a-Si:H Grown by HOMOCVD*,” J. Kanicki, C.M. Ransom, W. Bauhofer, T.I. Chappell and B.A. Scott, March 22-24, 1984, Bloomfield Hills, MI.
12. **International Conference on Optical Effects in Solids**, “*Photoconductivity of Intrinsic and Doped a-Si:H from 0.1 to 0.9 eV*,” T. Inushima, M.H. Brodsky, J. Kanicki and R.J. Serino, August 1-4, 1984, Salt Lake City, UT.
13. **International Conference on the Physics of Semiconductors**, “*Schottky Barrier Formation at Metal-Hydrogenated Amorphous Silicon Interfaces*,” J. Kanicki, M. Osama Aboelfotoh and W. Bauhofer, April 6-10, 1984, San Francisco, CA.
14. **1985 Materials Research Society Meeting**, “*Minority Carrier Injection and Series Resistance Effects in Hydrogenated Amorphous Silicon Schottky Diode*,” J. Kanicki, April 15-18, 1985, San Francisco, CA.

15. **167th Electrochemical Society Meeting**, “*Contact Properties of Metal Polyacetylene Interfaces*,” J. Kanicki, May 12-17, 1985, Toronto, Canada.
16. **11th International Conference on Amorphous and Liquid Semiconductors**, “*Optical, Electrical and Contact Properties of HOMOCVD a-Si:H Films*,” J. Kanicki, B.A. Scott, T. Inushima and M.H. Brodsky, September 2-6, 1985, Rome, Italy.
17. **1986 Materials Research Society Meeting**, “*Chemical and Mechanical Properties of Hydrogenated Amorphous Silicon Nitride Films Deposited in Various Systems*,” J. Kanicki and N. Voke, April 15-19, 1986, Palo Alto, CA.
18. **1986 Materials Research Society Meeting**, “*Optical and Electrical Properties of Hydrogenated Amorphous Silicon Nitride Films Deposited in Various Systems*,” J. Kanicki and N. Voke, April 15-19, 1986, Palo Alto, CA.
19. **1986 Materials Research Society Meeting**, “*Ohmic and Quasi-Ohmic Contacts to Hydrogenated Amorphous Silicon Thin Films*,” J. Kanicki and D. Bullock, April 15-19, 1986, Palo Alto, CA.
20. **1986 Metallurgical Society Northeast Regional Meeting**, “*Metallization to Hydrogenated Amorphous Silicon Thin Films*,” J. Kanicki, May 1-2, 1986, Murray Hill, NJ.
21. **170th Electrochemical Society Meeting**, “*Comparative Study of PECVD Nitride Films*,” J. Kanicki and P. Wagner, October 19-24, 1986, San Diego, CA.
22. **172nd Electrochemical Society Meeting**, “*Stable Photoinduced Paramagnetic Defects in Hydrogenated Amorphous Silicon Nitride*,” D. T. Krick, P. M. Lenahan, and J. Kanicki, October 18-23, 1987, Honolulu, HA.
23. **Tenth International Conference on Chemical Vapor Deposition**, “*Comparative Study of Silicon Dioxide Films Deposited by Various Techniques*,” J. Kanicki, D. B. Buchanan, and B. Robinson, October 18-23, 1987, Honolulu, HA.
24. **First Workshop on Process-Related Electrically Active Defects in Semiconductor Systems**, “*Stable Photo-Induced Paramagnetic Defects in Hydrogenated Amorphous Silicon Nitride*,” D.T. Krick, P. M. Lenahan, and J. Kanicki, September 1-2, 1987, Microelectronic Center of North Carolina Research Triangle Park, NC.
25. **1987 IEEE Semiconductor Interface Specialists Conference**, “*Stable Photoinduced Paramagnetic Defects in Silicon Nitride*,” D.T. Krick, P.M. Lenahan and J. Kanicki, December 3-5, 1987, Ft. Lauderdale, FL
26. **SPIE Meeting on Spectroscopic Characterization Techniques for Semiconductor Technology III**, “*Electron Spin Resonance Spectroscopy of Defects in Low Temperature Dielectric Films*,” D. Jousse, J. Kanicki, J. Batey, J. Stathis and Y. Cros, March 13-18, 1988, Newport Beach, CA.
27. **1988 March Meeting of the American Physical Society**, “*Induced Instabilities in Silicon Nitride*,” D.T. Krick, P.M. Lenahan and J. Kanicki, March 21-25, 1988, New Orleans, LA.
28. **1988 Materials Research Society Spring Meeting**, “*Role of Hydrogen in Silicon Nitride Films Prepared by Various Deposition Techniques*,” J. Kanicki, April 5-8, 1988, Reno, NV.
29. **1988 Materials Research Society Spring Meeting**, “*Temperature Dependent Characteristics of Hydrogenated Amorphous Silicon Thin Film Transistor*,” N. Lustig, J. Kanicki, R. Wisnieff and J. Griffith, April 5-8, 1988, Reno, NV.

30. **1988 IEEE Int. Symp. on Electrical Insulation**, “*Intrinsic Stress in Silicon Nitride and Silicon Dioxide Films Prepared by Various Deposition Techniques*,” J. Kanicki, P. Wagner, J. Karasinski and J. Angielello, June 5-8, 1988, Boston, MA.
31. **Rocky Mountain Conference**, “*Nature of the Dominant Deep Trap in Amorphous Silicon Nitride*,” D.T. Krick, P.M. Lenahan and J. Kanicki, August 3, 1988, Denver, CO.
32. **1988 Electrochemical Society Fall Meeting**, “*Nature of the Dominant Deep Trap in Amorphous Silicon Nitride*,” D.T. Krick, P.M. Lenahan and J. Kanicki, October 9-14, 1988, Chicago, IL.
33. **1988 Electrochemical Society Fall Meeting**, “*High Quality Nitrogen-Rich PECVD $a\text{-SiN}_x\text{:H}$ Films For Application in Thin Film Transistors*,” W.S. Lau, S.J. Fonash and J. Kanicki, October 9-14, 1988, Chicago, IL.
34. **1988 Electrochemical Society Fall Meeting**, “*Mobile Ion Drift in High Quality PECVD $a\text{-SiO}_x\text{:H}$ Films*,” G. Liu, W.S. Lau, S.J. Fonash and J. Kanicki, October 9-14, 1988, Chicago, IL.
35. **International Topical Conference on Hydrogenated Amorphous Silicon Devices and Technology**, “*Nature of the Dominant Deep Trap in Amorphous Silicon Nitride*,” W.S. Lau, G. Liu, S.J. Fonash and J. Kanicki, November 21-23, 1988, Yorktown Heights, NY.
36. **International Topical Conference on Hydrogenated Amorphous Silicon Devices and Technology**, “*An Investigation of Mobile Ion-Like Instability in High Quality Nitrogen-Rich $a\text{-SiN}_x\text{:H}$ Films and High Quality $a\text{-SiO}_x\text{:H}$ Films Deposited by PFCVD*,” W.S. Lau, G. Liu, S.J. Fonash and J. Kanicki, November 21-23, 1988, Yorktown Heights, NY.
37. **International Topical Conference on Hydrogenated Amorphous Silicon Devices and Technology**, “*A TEM Study of Low Temperature Crystallized Amorphous Silicon Films*,” G. Liu, W.S. Lau, R. Kakkad, S.J. Fonash and J. Kanicki, November 21-23, 1988, Yorktown Heights, NY.
38. **International Topical Conference on Hydrogenated Amorphous Silicon Devices and Technology**, “*Direct Observation of Hydrogenated Amorphous Silicon / Silicon Nitride Interface States Distributed Within the Hydrogenated Amorphous Silicon Bandgap*,” A.V. Gelatos and J. Kanicki, November 21-23, 1988, Yorktown Heights, NY.
39. **1988 Materials Research Society Fall Meeting**, “*Nature of the Dominant Deep Trap in Amorphous Silicon Nitride*,” D. T. Krick, P. M. Lenahan and J. Kanicki, November 28- December 3, 1988, Boston, MA.
40. **1989 American Physical Society Spring Meeting**, “*Origin of Light Induced Effects in Silicon Nitride*,” J. Kanicki, D. Jousse and J.H. Stathis, March 20-24, 1989, St. Louis, MO.
41. **1989 American Physical Society Spring Meeting**, “*Observation of Multiple Defect Configurations in Silicon Nitride*,” D. Jousse, J. Kanicki and J. H. Stathis, March 20-24, 1989, St. Louis, MO.
42. **Int. Conf. on Insulating Films on Semiconductors**, “*Electron Spin Resonance Study of Metal-Nitride-Silicon Structures: Observation of Si Dangling Bonds with Different Configurations and Trapping Properties in Silicon Nitride*,” D. Jousse, J. Kanicki and J. H. Stathis, March 29-31, 1989, Munich, Germany.

43. **Int. Conf. on Insulating Films on Semiconductors**, “*The Nature of the Dominant Deep Trap in Amorphous Silicon Nitride Films: Evidence for a Negative Correlation Energy*,” D.T. Krick, P.M. Lenahan and J. Kanicki, March 29-31, 1989, Munich, Germany.
44. **1989 Materials Research Society Spring Meeting**, “*Properties of High Conductivity Phosphorous Doped Hydrogenated Microcrystalline Silicon and Application in Thin Film Transistor Technology*,” J. Kanicki, E. Hansan, J. Griffith, T. Takamori and J.C. Tsang, April 24-29, 1989, San Diego, CA.
45. **1989 Materials Research Society Spring Meeting**, “*Properties and Application of Undoped Hydrogenated Microcrystalline Silicon Thin Films*,” J. Kanicki, E. Hasan, D.F. Kotecki, T. Takamori and J.H. Griffith, April 24-29, 1989, San Diego, CA.
46. **1989 Materials Research Society Spring Meeting**, “*Investigation of the Interface Between Silicon Nitride and a-Si:H by Deep Level Transient Spectroscopy and Voltage Pulse Transient Photocapacitance*,” A.V. Gelatos and J. Kanicki, April 24-29, 1989, San Diego, CA.
47. **1989 Electrochemical Society Spring Meeting**, “*Comparison of Thermally Grown and Plasma-Enhanced Chemical Vapor Deposited Silicon Dioxide Gate Dielectrics for Polycrystalline Silicon TFT's*,” M.K. Hatalis, S. Vincelette, J. Kanicki and P. Wagner, May, 1989, Los Angeles, CA.
48. **1989 Electronic Materials Conf.**, “*The Nature of the Dominant Deep Trap in Amorphous Silicon Nitride Films: Evidence for a Negative Correlation Energy*,” D.T. Krick, P.M. Lenahan and J. Kanicki, June 21-23, 1989, Cambridge, MA.
49. **1989 Electronic Materials Conf.**, “*Comparative Study of the Silicon Nitride Amorphous Silicon and Silicon Nitride Crystalline Silicon Interfaces*,” A.V. Gelatos and J. Kanicki, June 21-23, 1989, Cambridge, MA.
50. **13th Int. Conf. on Amorphous and Liquid Semiconductors**, “*Light Induced Effects in Hydrogenated Amorphous Nitrogen-Rich Silicon Nitride Films*,” J. Kanicki, D. Jousse, A. Gelatos and M.S. Crowder, August 21-25 1989, Asheville, NC.
51. **13th Int. Conf. on Amorphous and Liquid Semiconductors**, “*Investigation of the Silicon Nitride Amorphous Silicon Interface by Capacitance Measurements*,” A.V. Gelatos and J. Kanicki, August 21-25, 1989, Asheville, NC.
52. **9th Int. Symp. on Plasma Chemistry**, “*Properties of Device Quality Nitrogen-Rich Silicon Nitride Thin Films*,” J. Kanicki and D. Jousse, September 4-8, 1989, Pugnochiuso, Italy.
53. **1989 Materials Research Society Fall Meeting**, “*Correlations Between Structural, Electrical and Optical Properties of in-Situ Phosphorous Doped Hydrogenated Microcrystalline Silicon-Effects of Rapid Thermal Annealing on Material Properties*,” D.E. Kotecki, S.J. Jeng, C J. Kanicki, C. Park, W. Rausch, K. Seshan and J. Tien, November 27-30, 1989, Boston, MA.
54. **1990 American Physical Society March Meeting**, “*Photodarkening and Bleaching in Silicon Nitride*,” C.H. Seager and J. Kanicki, 12-16 March 1990, Anaheim, CA.
55. **1990 American Physical Society March Meeting**, “*Photo-bleaching of the LESR in Silicon Nitride*,” E.D. Tober, M.S. Crowder and J. Kanicki, 12-16 March 1990, Anaheim, CA.
56. **1990 American Physical Society March Meeting**, “*Evidence for a Negative Electron-Electron Correlation Energy in the Dominant Deep Trapping Center in Silicon Nitride Films*,” S.E. Curry, P.M. Lenahan, D.T. Krick and J. Kanicki, 12-16 March, 1990, Anaheim CA.

57. **1990 Materials Research Society Spring Meeting**, “*Electron Spin Resonance in Nitrogen-Rich Gate-Quality Amorphous Silicon Nitride: Photoproduction, Photodepletion and Thermal Annealing*,” E.D. Tober, M.S. Crowder and J. Kanicki, April 16-21, 1990, San Francisco, CA.
58. **1990 Materials Research Society Spring Meeting**, “*The Creation of Positive Charges in Gate-Quality Nitrogen-Rich Amorphous Silicon Nitride by Subbandgap UV-illumination*,” J. Kanicki and M. Sankaran, April 16-21, 1990, San Francisco, CA.
59. **1990 Materials Research Society Spring Meeting**, “*Effect of Gate Dielectric on Performance of Polysilicon Thin Film Transistors*,” M.K. Hatalis, J. Kung, J. Kanicki and A.A. Bright, April 16-21, 1990, San Francisco, CA.
60. **20th Int. Conf. on the Physics of Semiconductors**, “*Metastable Changes in Silicon Nitride Amorphous Silicon Structures Induced by Bias-Temperature Stress*,” J. Kanicki and A. Gelatos, August 6-10, 1990 Thessaloniki, Greece.
61. **20th Int. Conf on the Physics of Semiconductors**, “*The Generation and Photobleaching of Light Induced Positive Charge in Amorphous Silicon Nitride by Subbandgap UV-illumination*,” J. Kanicki and M. Sankaran, August 6-10, 1990, Thessaloniki, Greece.
62. **1990 IEEE Semiconductor Interface Specialists Conference**, “*Magnetic Resonance Investigation of Silicon and Nitrogen Dangling Bonds in Silicon Nitride*,” W.L. Warren, P.M. Lenahan and J. Kanicki, December 6-8, 1990, San Diego, CA.
63. **1991 American Physical Society March Meeting**, “*Paramagnetic Nitrogen Defects in Silicon Nitride*,” W.L. Warren, P.M. Lenahan, F.C. Rong, E.H. Poindexter and J. Kanicki, March 18-22, 1991, Cincinnati, OH.
64. **1991 American Physical Society March Meeting**, “*Kinetics of Photoinduced Trapping and Detrapping of Carriers in Amorphous Silicon Nitride Films*,” J. Kanicki, M. Sankaran, E.D. Tober, and M.S. Crowder, March 18-22, 1991, Cincinnati, OH.
65. **1991 Materials Research Society Spring Meeting**, “*Influence of the Gate Bias and Temperature on Positive Charge Generation in TFT Gate Quality Amorphous Silicon Nitride Films*,” J. Kanicki and M. Sankaran, April 29-May 3, 1991, Anaheim, CA.
66. **179th Electrochemical Society Meeting**, “*Hydrogenation of Polycrystalline Silicon Thin Film Transistors*,” M K. Hatalis, J.H. Kung and J. Kanicki, May 5-10, 1991, Washington, D.C.
67. **1991 Materials Research Society Spring Meeting**, “*Bias Stress Induced Instabilities in Amorphous Silicon Nitride/Polycrystalline Silicon and Amorphous Silicon Nitride / Amorphous Silicon Structures*,” J. Kanicki, C. Godet and A.V. Gelatos, April 29-May 3, 1991, Anaheim, CA.
68. **1991 Materials Research Society Spring Meeting**, “*Thermal Annealing of Light-Induced K-Centers in Hydrogenated Amorphous Silicon Nitride*,” E.D. Tober, E. Sigari, J. Kanicki and M.S. Crowder, April 29-May 3, 1991, Anaheim, CA.
69. **Int. Workshop on Science and Technology of Thin Films for 21st Century**, “*Investigations of Polysilicon Film Gate Dielectric Interface and Polysilicon Grain Size of Polycrystalline Silicon Thin Film Transistors*,” J. Kung, F. Lin M. Hatalis and J. Kanicki, July 28-August 2, 1991, Northwest University, Evanston, IL.

70. **14th Int. Conf. on Amorphous Semiconductors - Science and Technology**, “*Silicon Dangling Bond Centers in Amorphous Silicon Nitride*,” P.M. Lenahan, D.T. Krick, W.L. Warren and J. Kanicki, August 19-23, 1991, Garmisch-Partenkirchen, Germany.
71. **14th Int. Conf. on Amorphous Semiconductors - Science and Technology**, “*Microscopic Origin of the Light-Induced Defects in Hydrogenated Nitrogen-Rich Amorphous Silicon Nitride Films*,” J. Kanicki, W.L. Warren, C.H. Seager, M.S. Crowder and P.M. Lenahan, August 19-23, 1991, Garmisch-Partenkirchen, Germany.
72. **14th Int. Conf. on Amorphous Semiconductors - Science and Technology**, “*Determination of Electron and Hole Mobilities in a-Si:H from Photo-electric Effects in Waveguide Structure*,” M. Zelikson, K. Weiser, J. Salzman and J. Kanicki, August 19-23, 1991, Garmisch-Partenkirchen, Germany.
73. **14th Int. Conf. on Amorphous Semiconductors - Science and Technology**, “*Transient Photocapacitance and Capacitance Studies of Interface and Bulk States in Metal a-SiN_{1.6}:H / a-Si:Hc-Si Devices*,” G. Godet, J. Kanicki and A. Gelatos, August 19-23, 1991, Garmisch-Partenkirchen, Germany.
74. **1991 Materials Research Society Fall Meeting**, “*Optically Induced Paramagnetism in Amorphous Silicon Nitride*,” W.L. Warren, J. Kanicki, F.C. Rong, W.R. Buchwald, and M. Harmatz, December 2-6, 1991, Boston, MA.
75. **1991 Materials Research Society Fall Meeting**, “*Structure, Characteristics, and the Application of Phosphorous Doped Hydrogenated Microcrystalline Silicon*,” S.J. Jeng, D.E. Kotecki, J. Kanicki, and C.C. Parks, December 2-6, 1991, Boston, MA.
76. **22nd IEEE Semiconductor Interface Specialists Conf.**, “*Charge Trapping Centers in Silicon Nitride Thin Films*,” W.L. Warren, J. Kanicki, J. Robertson, E.H. Poindexter, C.H. Seager, and R.C. McWhorter, December 11-14, 1991, Lake Buena Vista, IL.
77. **Int. Semicon Device Research Symposium**, “*Photocapacitance and Conductance Studies of Silicon Nitride/Crystalline Silicon Interface States Produced by Bias-Stressing*,” C. Godet and J. Kanicki, December 4-6, 1991, Charlottesville, VA.
78. **1992 American Physical Society March Meeting**, “*Influence of Built-in Fields on the Electro-Optic Effect in an Amorphous Silicon Waveguide*,” M. Zelikson, K. Weiser, J. Sultzman and J. Kanicki, 16-20 March, 1992, Indianapolis, IN.
79. **1992 Materials Research Society Spring Meeting**, “*Investigation of Hydrogen and Nitrogen Stability in PEVCD a-SiN_x:H*,” D. Chen, J.M. Viner, P.C. Taylor and J. Kanicki, 27 April-1 May, 1992, San Francisco, CA.
80. **1992 Materials Research Society Spring Meeting**, “*Investigation of Hydrogen and Nitrogen Stability in PEVCD a-SiN_x:H*,” M. Fitzner, J.R. Abelson and J. Kanicki, April 27-May 1, 1992, San Francisco, CA.
81. **CLEO'92**, “*Electrooptic Effect in an Amorphous Silicon Core Waveguide Structure*,” M. Zelikson, J. Sultzman, K. Weiser and J. Kanicki, May 10-15, 1992, Anaheim, CA.
82. **181st Electrochemical Society Meeting**, “*Optically Induced Nitrogen Dangling Bonds in Amorphous Silicon Nitride Thin Films*,” W.L. Warren, J. Kanicki, R.C. McWhorter and E.H. Poindexter, May 17-22, 1992, St. Louis, MS.

83. **7th Trieste Semicon. Symp. On Wide-Band Gap Semiconductors**, “*Photocreation and Photobleaching of $a\text{-SiN}_{1.6}:\text{H}$ / $c\text{-Si}$ Interface States Studied by Photocapacitance Transient Spectroscopy*,” D. Godet and J. Kanicki, June 8-12, 1992, Trieste, Italy.
84. **50th Annual Device Research Conf.**, “*Hydrogenation Effects on Polysilicon Thin Film Transistor Structures*,” M.K. Hatalis, J.H. Kung and J. Kanicki, June 22-24, 1992, Boston, MA.
85. **21st Int. Conf. on the Physics of Semiconductors**, “*Electro-optic Effects in an Amorphous Silicon Waveguide*,” M. Zelikson, J. Sultzman, K. Weiser and J. Kanicki, August 10-14, 1992, Beijing, China.
86. **Int. Conf. on Solid State Devices and Materials**, “*A Simple Polysilicon Thin Film Transistor Structure for Achieving High On/Off Current Ratio Independent of Gate Bias*,” J. Kanicki and M. Hatalis, August 26-28, 1992, Tsukuba, Japan.
87. **Int. Conf. on Solid State Devices and Materials**, “*Bias-Stress Induced Stretched-Exponential Time Dependence of Charge Injection and Trapping in Amorphous Silicon Thin Film Transistors*,” F.R. Libsch and J. Kanicki, August 26-28, 1992, Tsukuba, Japan.
88. **Int. Conf. on Solid State Devices and Materials**, “*Nitrogen Dangling Bonds in Hydrogenated Amorphous Silicon Nitride Thin Films*,” J. Kanicki, W.L. Warren and E.H. Poindexter, August 26-28, 1992, Tsukuba, Japan.
89. **12th Int. Display Research Conf.**, “*A New Threshold Voltage Shift Estimation Method for Bias Temperature Stress of Amorphous Silicon Thin Film Transistors*,” F.R. Libsch and J. Kanicki, October 12-14, 1992, Hiroshima, Japan.
90. **39th Nat. American Vacuum Society Symp. & Topical Confs.**, “*Investigation of Hydrogen and Nitrogen Thermal Stability in PECVD $a\text{-SiN}_x:\text{H}$* ,” M. Fitzner, J.R. Abelson and J. Kanicki, November 9-13, 1992, Chicago, IL.
91. **1992 Materials Research Society Fall Meeting**, “*Experimental Evidence for Correlation Energy of Defect Centers in N-rich Hydrogenated Amorphous Silicon Nitride*,” J. Kanicki, W.L. Warren and C.H. Seager, November 30-December 4, 1992, Boston, MA.
92. **1992 Materials Research Society Fall Meeting**, “*The Effect of UV Light on the Infra-red Absorption Properties of Chemically Vapor Deposited $a\text{-SiN}_x:\text{H}$ Films*,” C.H. Seager and J. Kanicki, November 30 - December 4, 1992, Boston, MA.
93. **1992 Materials Research Society Fall Meeting**, “*Paramagnetic Nitrogen Defects in Silicon Nitride*,” W.L. Warren, J. Kanicki, J. Robertson and E.H. Poindexter, November 30-December 4, 1992, Boston, MA.
94. **1992 Materials Research Society Fall Meeting**, “*Performance of Polycrystalline Silicon Thin Film Transistors with Double Layer Gate Dielectric*,” J.H. Kung, M. Hatalis and J. Kanicki, November 30-December 4, 1992, Boston, MA.
95. **23rd IEEE Semicon. Interface Specialists Conf.**, “*Nitrogen Defect Centers in Silicon Nitride Thin Films*,” W.L. Warren, J. Kanicki, J. Robertson, R.C. McWhorter and E.H. Poindexter, December 9-12, 1992, San Diego, CA.
96. **1993 Society for Information Display Meeting**, “*TFT Lifetime in LCD Operation*,” F.R. Libsch and J. Kanicki, May 16-21, 1993, Seattle, WA.

97. **1993 Society for Information Display Meeting**, “*Low Temperature Poly-Si TFTs on Corning Code 1734 and 1735 Glass Substrates*,” M.K. Hatalis, D.N. Kouvatsos, J.-H. Kung, A.T. Voutsas, F.R. Fehlner and J. Kanicki, May 16-21, 1993, Seattle, WA.
98. **Active-Matrix Liquid-Crystal Displays Symposium**, “*DC and Pulsed Reliability of a-Si:H TFTs in XGA LCD Operation*,” E.F. Libsch and J. Kanicki, October 21-22, 1993, Bethlehem, PA.
99. **Active-Matrix Liquid-Crystal Displays Symposium**, “*Effect of Grain Size and Device Structure on Poly-Si TFT Performance*,” M.K. Hatalis, D.N. Kouvatsos, J.-H. Kung, S.H. Lin and J. Kanicki, October 21-22, 1993, Bethlehem, PA.
100. **1994 Materials Research Society Spring Meeting**, “*Photobleaching of PL and Temperature Dependence of EPR in Nitrogen-Rich Amorphous Silicon Nitride Films*,” D. Chen, J.M. Viner, P.C. Taylor, and J. Kanicki, April 4-8, 1999, San Francisco, CA.
101. **1994 European Materials Research Society Spring Meeting**, “*Nature of the Si and N Dangling Bonds in Silicon Nitride*,” J. Roberson, W.L. Warren and J. Kanicki, May 24-27, 1994, Strasbourg, France.
102. **1994 European Materials Society Spring Meeting**, “*Measurements of Interface States in Top Gate a-SiN_x:H / a-Si:H Structures*,” J. Kanicki and S. Backert, May 24-27, 1994, Strasbourg, France.
103. **1995 Int. Conf. on Solid State Devices and Materials**, “*Interface States in Top Gate Metal-Silicon Nitride-Silicon Structures*,” J. Kanicki, S. Backert and N. Picard, August 21-27, 1995, Osaka, Japan.
104. **1995 Int. Workshop on Active-Matrix Liquid-Crystal Displays**, “*UV-Light Induced Changes in Polyimide LC Alignment Films*,” J.Lu, S. Deshpande, J. Kanicki, A. Lien, R.A. John, and W.L. Warren, August 24-25, 1995, Osaka, Japan.
105. **1995 Int. Workshop on Active-Matrix Liquid-Crystal Displays**, “*Simulation of the High Performance a-Si:H TFT for High Definition LCDs*,” C.-Y. Chen and J. Kanicki, August 24-25, 1995, Osaka, Japan.
106. **2nd Int. Workshop on Active-Matrix Liquid-Crystal Displays**, “*Simulation of Influence of Density of States in a-Si:H on Electrical Performance of a-Si:H Thin Film Transistors*,” C.-Y. Chen and J. Kanicki, September 25-26, 1995, Bethlehem, PA.
107. **2nd Int. Workshop on Active-Matrix Liquid-Crystal Displays**, “*Electrical Performance of Top-Gate Amorphous Silicon Thin Film Transistors*,” C.-S. Chiang, J. Kanicki and F.R. Libsch, September 25-26, 1995, Bethlehem, PA.
108. **2nd Int. Workshop on Active-Matrix Liquid-Crystal Displays**, “*An Alternative Transparent Conducting Oxide to ITO for the a-Si:H TFT-LCD Applications*,” J.-H. Lan and J. Kanicki, September 25-26, 1995, Bethlehem, PA.
109. **2nd Int. Workshop on Active-Matrix Liquid-Crystal Displays**, “*Investigation of Hydrogen Evolution and Dangling Bonds Creation Mechanism in Amorphous Silicon Nitride Thin Films*,” T. Li, J. Kanicki, M. Fitzner, and W.L. Warren, September 25-26, 1995, Bethlehem, PA.
110. **1996 Materials Research Society Spring Meeting**, “*Selective Deposition of Polysilicon at Low Temperature by Hot-Wire CVD*,” S. Yu, E. Gulari and J. Kanicki, April 8-12, 1996, San Francisco, CA.

111. **1996 Materials Research Society Spring Meeting**, "*Atomic Hydrogen Effects on the Optical and Electrical Properties of Transparent Conducting Oxides for Flat Panel Displays*," J.-H. Lan and J. Kanicki, April 8-12, 1996, San Francisco, CA.
112. **1996 Materials Research Society Spring Meeting**, "*Influence of the Density of States and Temperature-Dependent Contact Resistance on the Field-Effect Activation Energy in a-Si:H TFT*," C.-Y. Chen and J. Kanicki, April 8-12, 1996, San Francisco, CA.
113. **1996 Materials Research Society Spring Meeting**, "*Poly (Bithiazoles): A New Class of Polymers for Light-Emitting Diodes*," D. Curtis, J.K. Politis, J. Nanos, and J. Kanicki, April 8-12, 1996, San Francisco, CA.
114. **1996 Materials Research Society Spring Meeting**, "*High-Rate Deposited Amorphous Materials for the Hydrogenated Amorphous Silicon Thin Film Transistor Structures*," T. Li, C.-Y. Chen, J. Kanicki and C. Malone, April 8-12, 1996, San Francisco, CA.
115. **IEEE 54th Device Research Conf.**, "*High Field-Effect Mobility a-Si:H TFT Based on High Deposition Rate Materials*," C.-Y. Chen and J. Kanicki, June 24-26, 1996, Santa Barbara, CA.
116. **16th Int. Display Research Conf.**, "*AMLCD Lifetime Evaluation Based on A.C. Electrical Instability of Amorphous Silicon Thin Film Transistors*," C.-S. Chiang, J. Kanicki, S. Nishida and K. Takechi, October 1-3, 1996, Birmingham, U.K.
117. **3rd Int. Display Workshops**, "*Electrical Performance and Instability of High Field Effect Mobility a-Si:H TFTs Made from High Deposition Rate PECVD Materials*," C.-Y. Chen, C.-S. Chiang, C. Malone and J. Kanicki, November 27-29, 1996, Kobe, Japan.
118. **3rd Int. Display Workshops**, "*a-Si:H TFT-LCD Lifetime Evaluation with Gate-Line Delay Consideration*," C.-S. Chiang, J. Kanicki, S. Nishida and K. Takechi, , November 27-29, 1996, Kobe, Japan.
119. **1996 Materials Research Society Fall Meeting**, "*Characterization of Instability in High-Rate Deposited Hydrogenated Amorphous Silicon Nitride Thin Films*," T. Li, C.-Y. Chen, J. Kanicki and C. Malone, December 2-6, 1996, Boston, MA.
120. **1997 SPIE Meeting, Symposium on Active Matrix Liquid Crystal Displays Technology and Applications**, "*Gated-Four-Probe TFT Structure: a New Technique to Measure the Intrinsic Performance of a-Si:H TFT*," C.-Y. Chen and J. Kanicki, Symposium on "Active Matrix Liquid Crystal Displays Technology and Applications," February 10-11, 1997, San Jose, CA.
121. **1997 Materials Research Society Spring Meeting**, "*Aluminum Gate Metallization for AMLCDs*," J.-H. Kim, J. Kanicki and W. den Boer, March 31-April 3, 1997, San Francisco, CA.
122. **1997 Materials Research Society Spring Meeting**, "*Electrical Characteristics of New LDD Poly-Si TFT with Mis-alignment Tolerant Structure for AMLCDs*," B.-H. Min and J. Kanicki, March 31 – April 3, 1997, San Francisco, CA.
123. **1997 Society for Information Display Int. Symp.**, "*Electric Stability of Short-Channel Poly-Si TFTs Fabricated by SPC and ELA for AMLCDs*," B.-H. Min, J.-H. Kim, J. Kanicki and G. Fortunato, May 13-15, 1997, Boston, MA.
124. **55th Device Research Conf.**, "*Gated-Four-Probe a-Si:H Thin-Film Transistor Structure*," C.-Y. Chen, C.-S. Chiang and J. Kanicki, June 23-25, 1997, Boulder, CO.

125. **1997 Int. Workshop on “Active-Matrix Liquid-Crystal Displays,”** “*Analysis of the Pixel Unit Cell Incorporating Planarization Polymer for the High-Aperture-Ratio a-Si:H TFT-LCDs,*” J.-H. Lan and J. Kanicki, September 11-12, 1997, Tokyo, Japan.
126. **1997 Int. Workshop on “Active-Matrix Liquid-Crystal Displays,”** “*Analysis of the Amorphous Silicon Thin Film Transistors Behavior Under Illumination,*” S. Martin, J. Kanicki, N. Szydlo and A. Rolland, September 11-12, 1997, Tokyo, Japan.
127. **1997 Int. Display Res. Conf.,** “*Aluminum Gate Metallization for High-Performance a-Si:H TFTs Fabricated from High-Deposition Rate PECVD Materials,*” C.-Y. Chen, B.-H. Min and J. Kanicki, September 15-19, 1997, Toronto, Canada.
128. **1997 Int. Display Res. Conf.,** “*Electrical Characteristics of Top-Gate a-Si:H TFTs for AMLCDs,*” C.-S. Chiang and J. Kanicki, September 15-19, 1997, Toronto, Canada.
129. **1997 Int. Display Res. Conf.,** “*Analysis of Amorphous Silicon Thin Film Transistors Behavior in the Dark and Under Illumination: Sensitivity to Geometric Parameters,*” S. Martin, J. Kanicki, N. Szydlo and Rolland, September 15-19, 1997, Toronto, Canada.
130. **1997 Int. Display Res. Conf.,** “*Planarization of Amorphous Silicon Thin Film Transistor for the High-Aperture-Ratio Active-Matrix Liquid-Crystal Displays,*” J.-H. Lan and J. Kanicki, September 15-19, 1997, Toronto, Canada.
131. **83rd Radiological Society of North America Meeting,** “*High Fidelity Electronic Display of Digital Radiographs,*” M.J. Flynn, J. Kanicki, A. Badano and W.R. Eyler, November 1997, Chicago, IL.
132. **1998 SPIE Int. Symp. on Medical Imaging,** “*The Effect of Secondary Radiations on the Performance of Digital Radiographic Detectors,*” M.J. Flynn, S. Wilderman and J. Kanicki, February 21-27, 1998, San Diego, CA.
133. **1998 Materials Research Society Spring Meeting,** “*Effects of Ultraviolet-Light on Polyimide Films for Liquid Crystal Alignment,*” S. Gong, J. Kanicki, L. Ma and J.Z.Z. Zhong, April 13-17, 1998, San Francisco, CA.
134. **1998 Materials Research Society Spring Meeting,** “*Longitudinal Vibrational Absorption Modes of Hydrogenated Amorphous Silicon Nitride Thin Films,*” T. Li and J. Kanicki, April 13-17, 1998, San Francisco, CA.
135. **1998 Society for Information Display Int. Symp.,** “*Full-Color Light-emitting Devices Based on π - and σ -Conjugated Polymer Materials,*” R. Hattori, Y. He, J. Kanicki, T. Sugano and T. Fujiki, May 17-22, 1998, Anaheim, CA.
136. **1998 Society for Information Display Int. Symp.,** “*High-Performance Top-Gate a-Si:H TFTs for AMLCDs,*” C.-S. Chiang, S. Martin, J.-Y. Nahm, J. Kanicki, Y. Ugai, T. Yukawa and S. Takeuchi, May 17-22, 1998, Anaheim, CA.
137. **1998 Society for Information Display Int. Symp.,** “*UV-Light Modified Polyimide Films for Liquid-Crystal Alignment,*” S. Gong, J. Kanicki, L. Ma and J.Z.Z. Zhong, May 17-22, 1998, Anaheim, CA.
138. **56th Device Research Conf.,** “*Planarized Copper Gate Hydrogenated Amorphous Silicon Thin-Film Transistors for AM-LCDs,*” J.-H. Lan and J. Kanicki, June 22-24, 1998, Charlottesville, VA.
139. **1998 Int. Workshop on Active-Matrix Liquid-Crystal Displays,** “*A Novel Wide Viewing Angle Twisted-Nematic LCD Structure.*” S. Gong, G. Xu and J. Kanicki, July 9-10, 1998, Tokyo, Japan.

140. **1998 Int. Workshop on Active-Matrix Liquid-Crystal Displays**, “*A Novel Wide Viewing Angle Twisted-Nematic LCD Structure.*” S. Gong, G. Xu and J. Kanicki, July 9-10, 1998, Tokyo, Japan.
141. **1998 Int. Workshop on Active-Matrix Liquid-Crystal Displays (AM-LCD’98)**, “*A Novel Wide Viewing Angle Twisted-Nematic LCD Structure,*” S. Gong, G. Xu and J. Kanicki, July 9-10, 1998, Tokyo, Japan.
142. **1998 Int. Workshop on Active-Matrix Liquid-Crystal Displays**, “*Amorphous Silicon Thickness Dependence of Top-Gate Thin-Film Transistors,*” S. Martin, C.-S. Chiang, J. Kanicki, Y. Ugai, T. Yukawa and S. Takeuchi, July 9-10, 1998, Tokyo, Japan.
143. **1988 Int. Workshop on Active-Matrix Liquid-Crystal Displays (AM-LCD’98)**, “*Fully Planarized a-S:H TFTs for AM-LCDs,*” J.-H. Lan, J. Kanicki and M. Radler, July 9-10, 1998, Tokyo, Japan.
144. **1998 Int. Conf. On Solid State Devices and Materials**, “*Two-Dimensional Numerical Simulation of Solid-Phase-Crystallized Polysilicon TFT Characteristics,*” T.-K. Chou and J. Kanicki, September 7-10, 1998, Hiroshima, Japan.
145. **Flat Panel and Vehicle Display ’98**, “*Reflective AMLCs,*” J. Kanicki, S. Martin, J.-Y. Nahm and Y. Ugai, September 9-10, 1998, Ypsilanti, MI.
146. **18th Int. Display Res. Conf. (Asia Display ’98)**, “*Amorphous Silicon Thin-Film Transistor Active-Matrix Reflective Cholesteric Liquid Crystal Display,*” J.Y. Nahm, T. Goda, B.H. Min, T.K. Chou, J. Kanicki, X.Y. Huang, N. Miller, V. Sergan, P. Bos and J.W. Doane, September 28-October 1, 1998, Seoul, Korea.
147. **18th Int. Display Res. Conf. (Asia Display ’98)**, “*OLED Based Display for Automotive Applications,*” Y. He, S. Gong, R. Hatttori and J. Kanicki, September 28–October 1, 1998, Seoul, Korea.
148. **1998 Electrochemical Society Meeting**, “*On the Evolution of Defect-Related Structure in the X-ray Absorption Spectra of PECVD SiN_x Films,*” E.C. Paloura and J. Kanicki, November 1-6, 1998, Boston, MA.
149. **84th Radiological Society of North America Meeting**, “*Contrast Reduction from Ambient Light for Film, CRT, and AM-LCD Display Devices,*” M. Flynn, A. Badano and J. Kanicki, November 29-December 4, 1998, Chicago. IL.
150. **1999 SPIE Conf. on Electroactive Polymer Actuators and Devices**, “*Organic Polymer Light-Emitting Devices on the Plastic Substrates,*” Y. He, S. Gong and J. Kanicki, March 1-2, 1999, Newport Beach, CA.
151. **1999 Materials Research Society Spring Meeting**, “*A High-Voltage Hydrogenated Amorphous Silicon Thin-Film Transistor for Reflective Active-Matrix Cholesteric LCD,*” J.Y. Nahm, J.H. Lan, T.K. Chou, B.H. Min, T. Goda and J. Kanicki, April 5-9, 1999, San Francisco, CA.
152. **1999 Society for information Display Int. Symposium**, “*Small-Spot Contrast Measurements in High-Performance Displays,*” A. Badano, M.J. Flynn and J. Kanicki, May 18-20, 1999, San Jose, CA.
153. **41st Electronic Materials Conf.**, “*Highly Efficient Organic Polymer Light-Emitting Devices on Plastic Substrates,*” Y. He and J. Kanicki, June 30-July 2, 1999, Santa Barbara, CA.
154. **1999 Int. Workshop on “Active-Matrix Liquid-Crystal Displays,”** “*Electrical Instabilities of Top-Gate a-Si:H TFTs for AMLCDs,*” S. Martin, J. Kanicki and Y. Ugai, July 14-16, 1999, Tokyo, Japan.

155. **1999 Int. Workshop on “Active-Matrix Liquid-Crystal Displays,”** “*Buried Busline a-Si:H TFT Structures for AM-LCDs,*” J.-H. Lan, J.-Y. Nahm and J. Kanicki, July 14-16, 1999, Tokyo, Japan.
156. **The 19th Int. Display Res. Conf. (EuroDisplay ’99),** “*High-Efficiency Organic Polymer Light-Emitting Heterostructure Devices on Flexible Plastic Substrates,*” Y. He and J. Kanicki, September 6-9, 1999, Berlin, Germany.
157. **The 19th Int. Display Res. Conf. (EuroDisplay ’99),** “*Buried Busline Structure for Large-Area, High-Resolution, and High-Aperture-Ratio AM-LCDs,*” J.-H. Lan, J.-Y. Nahm and J. Kanicki, September 6-9, 1999, Berlin, Germany.
158. **The 19th Int. Display Res. Conf. (EuroDisplay ’99),** “*Top-Gate a-Si:H TFTs for AM-LCDs: a-Si:H Thickness Effect and Electrical Instabilities,*” S. Martin, J. Kanicki and Y. Ugai, September 6-9, 1999, Berlin, Germany.
159. **Society for information Display Conf. on “Vehicle Displays and Microsensors ’99,”** “*Planarization Technology of AMLCD,*” J.-H. Lan and J. Kanicki, September 22-23, 1999. Ypsilanti, MI.
160. **1999 OSA Meeting on “Organic Thin Films for Photonics Applications,”** “*Monte Carlo Modeling Method for Light Transport in Organic Thin Film Light-Emitting Devices,*” A. Badano and J. Kanicki, September 24-26, 1999, Santa Clara, CA.
161. **85th Radiological Society of North America Meeting,** “*Medical Imaging Displays Based on Active-Matrix Thin Film Organic Polymer Light Emitting Devices,*” A. Badano, J. Kanicki, Y. He and M.J. Flynn, November 28-December 3, 1999, Chicago. IL.
162. **1999 Int. Electron Devices Meeting,** “*Hydrogenated Amorphous Silicon Thin film Transistor Structure with the Buried Field Plate,*” J.-Y. Nahm, J.-H. Lan and J. Kanicki, December 5-8, 1999, Washington, D.C.
163. **2000 Device Research Conference,** “*Five-Terminal Amorphous Silicon Thin-Film Transistor Structure,*” S. Martin, Y. Feillens and J. Kanicki, June 19-21, 2000, Denver, CO.
164. **2000 SPIE’s Annual Meeting,** “*Materials and Device Structures for High-Performance OLEDs,*” Y. Hong, Z. Hong, and J. Kanicki, July 30-August 2, 2000, San Diego, CA.
165. **2000 SPIE’s Annual Meeting,** “*Polyfluorene Light Emitting Devices on Flexible Plastic Substrates,*” Y. He and J. Kanicki, July 31-August 2, 2000, San Diego, CA.
166. **Society for information Display, 20th Int. Display Research Conf.,** “*Organic Light Emitting Devices on Plastic Flexible Substrates: New Cathode and Light Emissive Materials,*” Y. Hong, Z. Hong, M.D. Curtis, and J. Kanicki, September 25-28, 2000, Palm Beach, FL.
167. **Society for information Display, 20th Int. Display Research Conf.,** “*Gate Planarized a-Si:H TFTs with the Silicon-Based Flowable Oxide,*” J. Kim and J. Kanicki, September 25-28, 2000, Palm Beach, FL.
168. **Society for Inf. Display, 20th International Display Research Conference,** “*Many Body Universal Approach to a-Si:H TFTs Electrical Instabilities,*” S. Martin, J.-Y. Nahm, J. Kim and J. Kanicki, September 25-28, 2000, Palm Beach, FL.
169. **Society for Inf. Display, 20th International Display Research Conference,** “*Five-Terminal Thin-Film Transistor Structure,*” S. Martin, Y. Feillens and J. Kanicki, September 25-28, 2000, Palm Beach, FL.

170. **Society for Inf. Display, 20th Int. Display Research Conf.**, “*Electrical Reliability of Two –and Four-a-Si:H TFT Pixel Electrode Circuits for Active-Matrix OLEDs*,” Y. He, R. Hattori and J. Kanicki, September 25-28, 2000, Palm Beach, FL.
171. **6th Int. Conf. on the Science and Technology of Display Phosphors**, “*Organic Polymer Light-Emitting Devices and Displays on Plastic Flexible Substrate*,” J. Kanicki, Y. He, Y. Hong, Z. He, Z. Hong, and A. Badano, November 6-8, 2000, San Diego, CA.
172. **2000 IEEE International Electron Device Meeting**, “*Fingerprint Imager Based on a-Si:H Active-Matrix Photo-Diode Arrays*,” J. Lan, A. Cole, J. VanZandt, A. Dickinson, F. Van de Ven, N. Bird, A. Badano and J. Kanicki, December 11-13, 2000, San Francisco, CA.
173. **IS&T / SPIE 13th Int. Symposium on Electronic Imaging 2001 – Science and Technology**, “*a-Si:H Pixel Electrode Circuits for AM-OLEDs*,” J. Kanicki, Y. He and R. Hattori, January 21-26, 2001, San Jose, CA.
174. **2001 IS&T / SPIE 13th Int. Symposium on Electronic Imaging – Science and Technology**, “*Characterization of Crosstalk in high-Resolution Active-Matrix Liquid Crystal Displays for Medical Imaging*,” A. Badano and J. Kanicki, Flat Panel Display Technology and Display Metrology II, January 22-23, 2001, San Jose, CA.
175. **Medical Imaging 2001, SPIE Annual Meeting**, “*Advanced Amorphous Silicon Thin Film Transistor Active-Matrix Organic Light-Emitting Displays Design for Medical Imaging*,” J. Kim and J. Kanicki, February 18-20, 2001, San Diego, CA.
176. **Medical Imaging 2001, SPIE Annual Meeting**, “*Color and Contrast Perception in Monochrome Medical Imaging Flat-Panel Displays*,” A. Badano and J. Kanicki, February 18-20, 2001, San Diego, CA.
177. **2001 Materials Research Society Spring Meeting**, “*Amorphous Silicon Thin Film Transistor Pixel Electrode Circuits for Active-matrix organic light-emitting displays*,” J. Kanicki and J. Kim, April 16-20, 2001, San Francisco, CA.
178. **2001 Materials Research Society Spring Meeting**, “*Amorphous Silicon Thin Film Transistor Pixel Electrode Circuits for Active-Matrix Organic Light-Emitting Displays*,” J. Kanicki, April 16-20, 2001, San Francisco, CA.
179. **2001 59th Device Research Conference**, “*Electrical Instabilities of Organic Polymer Thin-Film Transistors*,” S. Martin and J. Kanicki., June 25-27, 2001, Notre Dame, IN.
180. **2001 43rd Electronic Materials Conference**, “*Electrical Performances and Physics of Organic Polymer Thin Film Transistors*,” S. Martin and J. Kanicki, June 27-29, 2001, Notre Dame, IN.
181. **2001 Int. Workshop on “Active-Matrix Liquid Crystal Displays”**, “*Analog-Circuit Simulation of the Current-Programmed Active-Matrix Pixel Electrode Circuits Based on Poly-Si TFT for Organic Light-Emitting Displays*,” R. Hattori, Y. Kuroki and J. Kanicki, July 11-13, 2001, Tokyo, Japan.
182. **2001 46th SPIEs (The International Society for Optical Engineering) Annual Meeting**, “*High Performance Organic Polymer Light-Emitting Devices (OPLEDs) with Two-Stacked Double Layers on Flexible Plastic Substrates*,” Y. Hong and J. Kanicki, July 29-August 1, 2001, San Diego, CA.

183. **2001 46th SPIE's (The International Society for Optical Engineering) Annual Meeting**, "*Air-Stable Organic Polymer Red Light-Emitting Devices on Flexible Plastic Substrates*," Y. Hong, Z. He, S. Lee, and J. Kanicki, July 30-August 1, 2001, San Diego, CA.
184. **3rd Int. Conf. on "Electroluminescence of Molecular Materials and Related Phenomena"**, "*Optimization of Organic Polymer Red Light-Emitting Devices on Flexible Plastic Substrates*," Y. Hong, S. Lee, and J. Kanicki, September 5-8, 2001, Los Angeles, CA.
185. **3rd Int. Conf. on "Electroluminescence of Molecular Materials and Related Phenomena"**, "*Monte Carlo Simulation of Spectral Photon Emission of the Organic Polymer Light-Emitting Devices*," S. Lee, A. Badano, Y. Hong, and J. Kanicki, September 5-8, 2001, Los Angeles, CA.
186. **3rd Int. Conf. on "Electroluminescence of Molecular Materials and Related Phenomena"**, "*Active - Matrix Pixel Electrode Circuits for 500 dpi Organic Light-Emitting Displays*," J. Kim and J. Kanicki, September 5-8, 2001, Los Angeles, CA.
187. **Asia Display / IDW '01**, "*Organic Polymer Light-Emitting Devices on Flexible Plastic Substrates for AM-OLED*," Y. Hong, S. Lee, Z. He, and J. Kanicki, October 16-19, 2001, Nagoya, Japan.
188. **Medical Image Perception Conf. IX**, "*Optimal Color for Supra-Threshold and Threshold Contrast Perception*," A. Badano, J. Kim and J. Kanicki, September 20-23, 2001, Warrenton, VA.
189. **Asia Display / IDW '01**, "*Photosensitivity of a-Si:H TFTs*," J.-D. Gallezot, S. Martin and J. Kanicki, October 10-19, 2001, Nagoya, Japan.
190. **Asia Display / IDW '01**, "*Two Photo-Mask Fully Self-Aligned Al Bottom-Gate a-Si:H TFTs*," J.H. Kim and J. Kanicki, October 10-19, 2001, Nagoya, Japan.
191. **RSNA'01**, "*Angular Dependence of the Luminance and Contrast in Medical Imaging Monochrome Active-Matrix Liquid Crystal Displays*," A. Badano, M. Flynn, S. Martin and J. Kanicki, November 25-30, 2001, Chicago, IL.
192. **RSNA'01**, "*Image Quality Characterization of Medical Imaging Monochrome Active-Matrix Liquid Crystal Displays*," A. Badano, S. Martin and J. Kanicki, November 25-30, 2001, Chicago, IL.
193. **Medical Imaging 2002: Visualization, Image-Guided Procedures, and Display**, "*Amorphous Silicon Thin-Film Transistors-Based Active-Matrix Organic Light-Emitting Displays for Medical Imaging*," J.H. Kim and J. Kanicki, February 24-26, 2002, San Diego, CA.
194. **Medical Imaging 2002: Visualization, Image-Guided Procedures, and Display**, "*Characterization of a High Quality Monochrome AM-LCD Monitor for Digital Radiology*," S. Martin, A. Badano and J. Kanicki, February 24-26, 2002, San Diego, CA.
195. **2002 IMAPS (International Microelectronics and Packaging Society)**, Advanced Technology Workshop on Printing an Intelligent Future, "*Gate-Planarized Organic Polymer Thin-Film Transistors*," S. Martin, J. Kanicki, M. Dibbs, D. Brennan and D. Welsh, March 8-10, 2002, Lake Tahoe, NV.
196. **2002 Society for Information Display Int. Symp.**, "*Novel Poly-Si TFT Pixel Electrode Circuits and Current Programmed Active-Matrix Driving Methods for AM-OLEDs*," Y. Hong, R. Hattori, and J. Kanicki, May 21-23, 2002, Boston, MA.
197. **2002 Society for Information Display Int. Symp.**, "*Amorphous Silicon Thin-Film Transistors-Based Active-Matrix Organic Light-Emitting Display*," J. Kim and J. Kanicki, May 21-23, 2002, Boston, MA.

198. **Electron, Ion and Photo Beam, and Nanotechnology 2002**, “*Nanoimprinted Organic Polymer Light-Emitting Devices for AM-OP-LEDs*,” X. Cheng, Y. Hong, J. Kanicki, and L.J. Guo, May 28-30, 2002, Anaheim, CA.
199. **2002 SPIE’s (The International Society for Optical Engineering) Annual Meeting**, “*Integrating Sphere CCD-Based Measurement Method of the OP-LED Opto-Electronic Characteristics*,” Y. Hong and J. Kanicki, July 8-10, 2002, Seattle, WA.
200. **2002 SPIE’s (The International Society for Optical Engineering) Annual Meeting**, “*Mote Carlo Modeling of Organic Polymer Light-Emitting Devices on Flexible Plastic Substrates*,” S.J. Lee, A. Badano and J. Kanicki, July 8-10, 2002, Seattle, WA.
201. **2002 SPIE’s (The International Society for Optical Engineering) Annual Meeting**, “*Efficient and Saturated Blue Organic Polymer Light Emitting Devices with an Oxidiazole Containing Poly(fluorine) Polymer Emissive Layer*,” S.J. Lee, J.R. Gallegos, J. Klein, M.D. Curtis and J. Kanicki, July 8-10, 2002, Seattle, WA.
202. **2002 SPIE’s Annual Meeting**, “*Comparison Between Lens-Coupled and Integrating Sphere CCD-Based Measurement Methods of the OP-LED Optoelectronic Characteristics*,” Y. Hong and J. Kanicki, July 29-August 3, 2002, Seattle, WA.
203. **2002 SPIE’s Annual Meeting**, “*High-Resolution Transmission Electron Microscopy (HR-TEM) Study of the OP-LED Structures on Flexible Plastic Substrates*,” Y. Hong and J. Kanicki, July 29-August 3, 2002, Seattle, WA.
204. **2002 EL International Conf. on the Science and Technology of Emissive Displays and Lighting**, “*Three - Amorphous Silicon Thin-Film Transistors Active-Matrix Organic Polymer Light-Emitting Displays*,” J. Kim and J. Kanicki, September 23-26, 2002, Ghent, Belgium.
205. **DoD Breast Cancer Research Program Meeting**, “*Optimal Color for Supra-threshold and Threshold Contrast Perception*,” A. Badano, J.H. Kim and J. Kanicki, September 25-28, 2002, Orlando, FL.
206. **2002 EuroDisplay, The 22nd International Display Research Conf.**, “*Three - Amorphous Silicon Thin-Film Transistors-Based Active-Matrix Organic Polymer Light-Emitting Displays*,” J. Kim and J. Kanicki, October 2-4, 2002, Nice, France.
207. **2002 EuroDisplay, The 22nd International Display Research Conf.**, “*Organic Polymer Thin-Film Transistors for Active-Matrix Flat-Panel Displays?*” S. Martin and J. Kanicki, October 2-4, 2002, Nice, France.
208. **2002 EuroDisplay, The 22nd International Display Research Conf.**, “*High-Resolution Medical Imaging AM-LCD: Contrast Performance Evaluation*,” S. Martin, A. Badano and J. Kanicki, October 2-4, 2002, Nice, France.
209. **2002 EuroDisplay, The 22nd International Display Research Conf.**, “*Printed Micron-Scale Organic Polymer Light-Emitting Devices for AM-OPLED*,” Y. Hong, X. Cheng, L. Jay Guo and J. Kanicki, October 2-4, 2002, Nice, France.
210. **2003 MRS Spring Meeting**, “*Organic Polymer Devices Based on Super-Yellow Polymer*,” J. Kanicki, M. Pauchard and A. Heeger, April 21-25, 2003, San Francisco, CA.
211. **2003 Materials Research Society Spring Meeting**, “*Effect of Illumination on Organic Polymer Thin-Film Transistors*,” M.C. Hamilton, S. Martin and J. Kanicki, April 21-25, 2003, San Francisco, CA.

212. **2003 Materials Research Society Spring Meeting**, “*Source/Drain Contacts in Organic Polymer Thin Film Transistors*,” S. Martin, M. Hamilton and J. Kanicki, April 21-25, 2003, San Francisco, CA.
213. **Society for Information Display, 2003 Int. Symposium**, “*200 dpi 3-a-Si:H TFTs Voltage-Driven AM-PLEDs*,” J.-H. Kim and J. Kanicki, May 21-22, 2003, Baltimore, MD.
214. **Society for Information Display, 2003 Int. Symposium**, “*200 dpi 4-a-Si:H TFTs Current-Driven AM-PLEDs*,” Y. Hong, J.-Y. Nahm and J. Kanicki, May 21-22, 2003, Baltimore, MD.
215. **Society for Information Display, 2003 Int. Symposium**, “*Luminance Probes for contrast Measurements in Medical Displays*,” A. Badano, S. Pappada, E.F. Kelly, M.J. Flynn, S. Martin and J. Kanicki, May 21-22, 2003, Baltimore, MD.
216. **SPIE (The Int. Society for Optical Engineering) Meeting**, “*Organic Polymer Thin-Film Photo-Transistors*,” M.C. Hamilton, S. Martin and J. Kanicki, August 3-4, 2003, San Diego, CA.
217. **SPIE (The Int. Society for Optical Engineering) Meeting**, “*Time Dependence of Organic Polymer Thin-Film Transistors Current*,” S. Martin, L. Dassas, M.C. Hamilton and J. Kanicki, August 3-4, 2003, San Diego, CA.
218. **SPIE (The Int. Society for Optical Engineering) Meeting**, “*Influence of Gate Dielectric on the Electrical Properties of F8T2 Polyfluorene Thin-Film Transistors*,” J. Swensen, J. Kanicki and A.J. Heeger, August 3-4, 2003, San Diego, CA.
219. **SPIE (The Int. Society for Optical Engineering) Meeting**, “*Structural Ordering in F8T2 Polyfluorene Thin-Film Transistors*,” L. Kinder, J. Kanicki, J. Swensen and P. Petroff, August 3-4, 2003, San Diego, CA.
220. **23rd Int. Display Research Conf.**, “*Effect of Monochromatic Illumination on Organic Polymer Thin-Film Transistors*,” M.C. Hamilton, S. Martin and J. Kanicki, September 16-18, 2003, Phoenix, AZ.
221. **23rd Int. Display Research Conf.**, “*Electrical Instabilities of Organic Polymer Thin-Film Transistors*,” S. Martin, L. Dassas, M. Hamilton and J. Kanicki, September 16-18, 2003, Phoenix, AZ.
222. **23rd Int. Display Research Conf.**, “*Monte Carlo Simulations and Opto-Electronic Properties of Polymer Light-Emitting Devices on Flexible Plastic Substrates*,” S.J. Lee, A. Badano and J. Kanicki, September 16-18, 2003, Phoenix, AZ.
223. **Society of Information Display, 2005 Int. Symposium**, “*A Novel Current-Scaling a-Si:H TFTs Pixel Electrode Circuit for Active-Matrix Organic Light-Emitting Displays*,” Y.-C. Lin, H.-P. Shieh, C.-C. Su, H. Lee and J. Kanicki, May 24-27, 2005, Boston, MA.
224. **63rd Annual Device Research Conference**, “*Time and Temperature Dependence of the Drain Current of PF-based OFETs*,” M.C. Hamilton and J. Kanicki, June 20-22, 2005, Santa Barbara, CA.
225. **2005 Int. Conf. on Solid-State Devices and Materials**, “*White Light-Emitting Device on Flexible Plastic Substrates*,” H. Lee and J. Kanicki, September 13-15, 2005, Kobe, Japan.
226. **2005 MRS Fall Meeting**, “*Incorporating of Perovskite Oxides Into Gate Insulator of Zinc Oxide TFTs*,” J. Siddiqui, E. Cagin, P. Shea, J. Kanicki and J. Phillips, 2005, Boston, MA.
227. **Society for Information Display, 2006 Int. Symposium**, “*Current-Scaling a-Si:H TFT Pixel Electrode Circuit for AM-OLEDs*,” H. Lee, J. Kanicki, Y.C. Lin and H.-P. Shieh, June 7-9, 2006, San Francisco, CA.

228. **Electronic Materials Conf. 2006**, “Zinc Tetrabenzoporphyrins Organic Field-Effect Transistors,” P.B. Shea, J. Kanicki, M. Kawano, H. Yamada and N. Ono, June 28-30, 2006, State College, PA.
229. **13th Int. Workshop on “Active-Matrix Flat Panel Displays and Devices-TFT Technologies and Related Materials”**, “Novel Current-Scaling Current-Mirror *a*-Si:H TFT Pixel Electrode Circuit with Cascade Capacitor for AM-OLEDs,” H. Lee, J.-S. Yoo, C.-D. Kim, I.-J. Chung and J. Kanicki, July 5-7, 2006, Tokyo, Japan.
230. **Society for Information Display, 26th Int. Display Research Conference**, “Reliability Enhancement of AM-OLED with *a*-Si:H TFT and Top-Anode OLED Employing a New Pixel Circuit,” J.S. Yoo, H. Lee, J. Kanicki, C.-D. Kim and I.-J. Chung, September 18-21, 2006, Kent, OH.
231. **Society for Information Display, 2006 Vehicles and Photons Symposium**, “White Light-Emitting Device on Flexible Plastic Substrate,” H. Lee and J. Kanicki, October 12-13, 2006, Dearborn, MI.
232. **Society for Information Display, 2006 Vehicles and Photons Symposium**, “Low Temperature Encapsulation for PLEDs and OLEDs,” A.R. Johnson and J. Kanicki, October 12-13, 2006, Dearborn, MI.
233. **Society for Information Display, 2007 Vehicles and Photons Symposium**, “Novel Pixel Electrode Circuits and *a*-Si:H TFT Structures for AM-OLEDs,” H. Lee, J.S. Yoo, C.-D. Kim, I. Kang and J. Kanicki, October 11-12, 2007, Dearborn, MI.
234. **Society for Information Display, 2007 Vehicles and Photons Symposium**, “Low Temperature Encapsulation for OLEDs,” A.R. Johnson and J. Kanicki, October 11-12, 2007, Dearborn, MI.
235. **Society for Information Display, 2007 Vehicles and Photons Symposium**, “Thermal and Electrical Instability of Amorphous Silicon Thin-Film Transistors for AM-FPDs,” A. Kuo and J. Kanicki, October 11-12, 2007, Dearborn, MI.
236. **IDW '07 (The 14th International Display Workshop)**, “*a*-Si:H HEX-TFTs, a New Technology for Flat Panel Displays,” H. Lee, J.S. Yoo, C.-D. Kim, I.B. Kang and J. Kanicki, December 5-7, 2007, Sapporo, Japan.
237. **Society for Information Display, 2008 Int. Symposium**, “Photosensitivity of Amorphous IGZO TFTs for Active-Matrix Flat-Panel Displays,” C.-S. Chuang, T.-C. Fung, B. G. Mullins, K. Nomura, T. Kamiya, H.-P. D. Shieh, H. Hosono, and J. Kanicki, May 22, 2008, Los Angeles, CA.
238. **66th Annual Device Research Conf.**, “Study of the Density of States of *a*-InGaZnO Using Field-Effect Technique,” C. Chen, T.C. Fung, K. Abe, H. Kumomi and J. Kanicki, June 23-25, 2008, Santa Barbara, CA.
239. **AM-FPD 08, The Fifteenth International Workshop on Active-Matrix Flatpanel Displays and Devices**, “*a*-InGaZnO TFT Current-Scaling Pixel Electrode Circuit for AM-OLEDs,” C. Chen, K. Abe, T.C. Fung, H. Kumomi, and J. Kanicki, July 2-4, 2008, Tokyo, Japan.
240. **AM-FPD 08, The Fifteenth International Workshop on Active-Matrix Flatpanel Displays and Devices**, “2-D Numerical Simulation of High Performance Amorphous In-Ga-Zn-O TFTs for Flat Panel Displays,” T.C. Fung, C.S. Chuang, C. Chen, K. Abe, H. Kumomi and J. Kanicki, July 2-4, 2008, Tokyo, Japan.

241. **Society for Information Display–International Meeting (IMID 08, Digest of Technical Papers)**, “*Photofield-Effect in Amorphous InGaZnO TFTs*,” T.-C. Fung, C.-S. Chuang, B. G. Mullins, K. Nomura, T. Kamiya, H.-P. D. Shieh, H. Hosono, and J. Kanicki, October 13-17, 2008, KINTEX, Iisan, Korea.
242. **Society for Information Display, 2008 Vehicles and Photons Symposium**, “*PLD Amorphous In-Ga-Zn-O TFTs for Future Optoelectronics*,” T.-C. Fung, K. Nomura, H. Hosono, and J. Kanicki, October 16-17, 2008, Dearborn, MI.
243. **Society for Information Display, 2008 Vehicles and Photons Symposium**, “*RF Sputter a-InGaZnO Thin Film Transistors for Flat Panel Displays*,” C. Chen, K. Abe, H. Kumomi, J. Kumomi, and J. Kanicki, October 16-17, 2008, Dearborn, MI.
244. **The 28th International Display Research Conf.**, “*Current Temperature Stress Study of RF Sputter a-InGaZnO TFTs*,” C. Chen, K. Abe, H. Kumomi, J. Kumomi, and J. Kanicki, November 4-6, 2008, Orlando, FL.
245. **IDW '08 (The 15th International Display Workshop)**, “*Bias-Temperature Stress Study of R.F. Sputter Amorphous In-Ga-Zn-O TFTs*,” T.-C. Fung, K. Abe, H. Kumomi and J. Kanicki,” December 3-5, 2008, Niigata, Japan.
246. **SID (Society for Information Display), 2009 International Symposium**, “*DC / AC Electrical Instability of RF Sputter Amorphous In-Ga-Zn-O TFTs*,” T.-C. Fung, K. Abe, H. Kumomi and J. Kanicki, June 2-5, 2009, San Antonio, TX.
247. **SID (Society for Information Display), 2009 International Symposium**, “*AM-OLED Pixel Circuits Based on a-InGaZnO Thin Film Transistors*,” C. Chen, K. Abe, H. Kumomi and J. Kanicki, June 2-5, 2009, San Antonio, TX.
248. **29th International Display Research Conference, EuroDisplay 2009**, “*A Maskless Laser-Write Lithography Processing of Thin-Film Transistors*,” G. Yoo, W. Salewski, J. Herrmann and J. Kanicki September 14-17, 2009, Rome, Italy.
249. **29th International Display Research Conference, EuroDisplay 2009**, “*Electrical Stability of Hexagonal a-Si:H TFTs*,” G. Yoo, H. Lee and J. Kanicki, September 14-17, 2009, Rome, Italy.
250. **6th International Thin – Film Transistor Conference**, “*Threshold Voltage Control of the D.C. Sputtered Staggered Amorphous Indium-Gallium-Zinc Oxide Thin-Film Transistor*,” A. Kuo, K. Abe, H. Kumomi, and J. Kanicki, January 28 – 29, 2010, Egret, Himeji, Japan.
251. **SID (Society for Information Display), 2011 International Symposium**, “*Electrical Properties and Stability of Dual-Gate Coplanar Homojunction Amorphous Indium-Gallium-zinc-Oxide Thin – Film Transistor*,” G. Baek, A. Kuo, K. Abe, H. Kumomi and J. Kanicki, May 17 - 20, 2011, Los Angeles, CA.
252. **SID (Society for Information Display), 2011 Vehicles and Photons Symposium**, “*Analytical Models of Synchronized Dual-Gate a-IGZO TFTs*,” G. Baek and J. Kanicki, October 20 – 21, 2011, Dearborn, MI.
253. **Society for Information Display (SID) 2012 Symposium**, “*a-IGZO TFT Based Pixel Circuits for AM-OLED Displays*,” H. Jung, Y. Kim, C. Chen, J. Kanicki and H. Lee, June 5-8, 2012, Boston, MA.
254. **Active-Matrix Flat Panel Displays and Devices – TFT Technologies and FPD Materials**, “*CIGS Solar Cells on Flexible Stainless Steel Substrate Fabricated by Sputtering Method: Simulation and Experimental Results*,” Rui Zhang, Dennis R. Hollars and Jerzy Kanicki, The 19th International

Workshop on, July 4-6, 2012, Kyoto, Japan.

255. **Active-Matrix Flat Panel Displays and Devices – TFT Technologies and FPD Materials**, “*Scaling of a-InGaZnO TFTs and Pixel Electrode for AM-LCDs*,” Gwanghyeon Baek, Katsumi Abe, Hideya Kumomi and Jerzy Kanicki, The 19th International Workshop on July 4-6, 2012, Kyoto, Japan.
256. **2013 Society for Information Display (SID) Symposium**, “*AC and DC Bias-Temperature Stability of Coplanar Homojunction a-InGaZnO Thin-Film Transistors*,” Eric Kai-Hsiang Yu, Katsumi Abe, Hideya Kumomi and Jerzy Kanicki, May 21-24, 2013, Vancouver, Canada.
257. **2013 Device Research Conference (DRC)**, “*Dynamic Response of Amorphous In-Ga-Zn-O Thin-Film Transistors for 8kx4k Flat-Panel Display*.” Rui Zhang, Linsen Bie, Eric Yu and Jerzy Kanicki, June 23-26, South Bend, IN.
258. **20th International Workshop on Active-Matrix Flat Panel Displays and Devices: TFT Technologies and FPD Materials (AM-FPD 2013)**, “*A Novel a-InGaZnO TFT Based Voltage Programmed Pixel Circuit to Compensate Threshold Voltage and Mobility Variations*,” Yonchan Kim, Jerzy Kanicki and Hojin Lee, July 2-5, 2013, Kyoto, Japan.
259. **2013 IEEE International Device Meeting (IEDM)**, “*High Performance Amorphous Metal-Oxide Semiconductor Thin Film Passive and Active Pixel Sensor*,” Rui Zhang, Linsen Bie, Tze-Ching Fung, Eric Kai-Hsiang Yu, Chumin Zhao and Jerzy Kanicki, December 9-11, 2013, Washington, D.C.
260. **Society for Information Display (SID) 2014 Symposium**, “*Top Gate Amorphous In-Ga-Zn-O Thin Film Transistors Fabricated on Soda-lime-silica Glass Substrates*,” Gwanghyeon Bark, Alex Krasnov, Willem den Boer and Jerzy Kanicki, June 1-6, 2014, San Diego, CA.
261. **SID (Society for Information Display) 2014 Vehicles and Photons Symposium**, “*Dynamic Response of a-InGaZnO Thin-Film Transistors for Ultra-High Definition Active-Matrix Liquid Crystal Displays*,” Eric K.-H. Yu, Rui Zhang, Linsen Bie, Alex Kuo and Jerzy Kanicki, October 23-24, 2014, Dearborn, MI.